

GEORGE KONSTANTINIDIS

LIST OF PUBLICATIONS



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[1]. PUBLISHED WORK (RESEARCHER ID: A-1719-2014)

[1.1]. PUBLICATIONS IN REFEREED JOURNALS (WEB OF SCIENCE)

1. **Transferrable dielectric DBR membranes for versatile GaN-based polariton and VCSEL technology**
E.A. Amargianitakis, S.A.Kazazis, G.Doundoulakis, G.Stavrinidis, G.Konstantinidis, E.Delamadeleine, E.Monroy, N.T.Pelekanos
Microelectronic Engineering 228, 111276, Published 2020
<https://doi.org/10.1016/j.mee.2020.111276>
2. **Field emission induced damage in the actuation paths of MEMS capacitive structures**
J. Theocharis, M. Koutsourelis, S. Gardelis, G. Konstantinidis, G. Papaioannou
Microelectronics Reliability 114, 113760, Published 2020
<https://doi.org/10.1016/j.microrel.2020.113760>
3. **Thermally activated discharging mechanisms in SiNx films with embedded CNTs for RF MEMS capacitive switches**
M. Koutsourelis, G. Stavrinidis, D. Birbilitis, G. Konstantinidis, G. Papaioannou
Microelectronic Engineering 223, 111230, Published 2020
DOI: 10.1016/j.mee.2020.111230
4. **On the discharge transport mechanisms through the dielectric film in MEMS capacitive switches**
D. Birbilitis, G. Stavrinidis, M. Koutsourelis, G. Konstantinidis, G. Papaioannou
IEEE/ASME Journal of microelectromechanical systems 29, 202, Published 2020
DOI: 10.1109/JMEMS.2019.2962068
5. **Monolithic Intergrated Antenna and Schottky diode multiplier for free space millimeter wave power generation**
Al. Bunea, D. Neculoiu, A. Stavrinidis, G. Konstantinidis, G. Stavrinidis, A. Kostopoulos, Z. Chatzopoulos
IEEE microwave and wireless components letters, V30, Issue 1, 74, Published 2019
DOI:10/1109/LMWC.2019.2954208
6. **Epitaxially Oriented Sn:In₂O₃ Nanowires Grown by the Vapor–Liquid–Solid Mechanism on m-, r-, a-Al₂O₃ as Scaffolds for Nanostructured Solar Cells**
A. Charalambous, M. Zervos, J. Kioseoglou, K. Tsagaraki, M. Androulidaki, G. Konstantinidis, E. Tanasa, E. Vasile
ACS Appl. Energy. Mater. 2,6, 4274, Published 2019
DOI: 10.1021/acsaem.9b00519
7. **A comparative study of nanostructured Silicon-Nitride electrical properties for potential application in RF-MEMS capacitive switches**
D. Birbilitis, G. Stavrinidis, M. Koutsourelis, G. Konstantinidis, G. Papaioannou, A. Ziaei
Microelectronics Reliability, 113360, Published 2019
DOI: 10.1016/j.microrel.2019.06.052
8. **Quantum size effect in superconducting aluminum films**
K. Arutyunov, E. Sedov, I.A. Golokolenov, V.V. Zayalov, G. Konstantinidis, A. Stavrinidis, G. Stavrinidis, I. Vasiliadis, T. Kehagias, G.P. Dimitrakopoulos, F. Komninou, M.D. Kroituru, A.A. Shanenko
Physics of the Solid State, V61, 1559, Published 2019

9. Long-term stability of transparent n/p ZnO homojunctions grown by rf-sputtering at room-temperature

V. Kampylafka, A. Kostopoulos, M. Modreanu, M. Schmidt, E. Gagaoudakis, K. Tsagaraki, V. Kontomitrou, G. Konstantinidis, G. Deligeorgis, G. Kiriakidis, E. Aperathitis
Journal of Materiomics 5, 428, Published 2019
DOI: 10.1016/j.mat.219.02.006

10. Improved GaN quantum well microcavities for robust room temperature polaritronics

E. Amargianitakis, F. Miziou, M. Androulidaki, K. Tsagaraki, A. Kostopoulos, G. Konstantinidis, E. Delamadeleine, E. Monroy, N. Pelelanos
Physics Status Solidi B, 1800716, Published 2019
DOI: 10.1002/pssb.201800716

11. Nanofabrication of normally-off GaN vertical nanowire MESFETs

G. Doundoulakis, A. Adikimenakis, A. Stavrinidis, K. Tsagaraki, M. Androulidaki, F. Iacovella, G. Deligeorgis, G. Konstantinidis and A. Georgakilas
Nanotechnology 30 285304, Published 2019
DOI: 10.1088/1361-6528/ab13do

12. Experimental and modeling insight for fin-shaped transistors based on AlN/GaN/AlN double barrier heterostructure

G. Doundoulakis, A. Adikimenakis, A. Stavrinidis, K. Tsagaraki, M. Androulidaki, G. Deligeorgis, G. Konstantinidis, A. Georgakilas,
Solid State Electronics 158 1–10, Published 2019
DOI: 10.1016/j.sse2019.04.005

13. Nanoarchitecture: Toward Quantum-Size Tuning of Superconductivity

K.Y. Arutyunov, V. Zavialov, E.A Sedov, I.A Golokolenov, A.A. Zarudneva, I.N. Trun'kin, A. L. Vasiliev, G. Konstantinidis, A. Stavrinidis, G. Stavrinidis, M.D. Croitoru, A. A. Shanenko
Phys. Status Solidi RRL (Nanosized superconductors), 1800317, Published: 2018
DOI: 10.1002/pssr.201800317

14. Cross-Section Doping Topography of 4H-SiC VJFETs by Various Techniques

K. Tsagaraki, M. Nafouti, H. Peyre, K. Vamvoukakis, N. Makris, M. Kayambaki, A. Stavrinidis, G. Konstantinidis, M. Panagopoulou, D. Alquier, K. Zekentes
Materials Science Forum 924, pp. 653-656, Published: 2018
DOI: 10.4028/www.scientific.net/MSF.924.653

15. A Continuous Semi-Empirical VJFET Capacitance Model from Sub to above Threshold Regime

N. Makris, M. Kayambaki, , A. Stavrinidis, G. Konstantinidis, G. Zekentes
Materials Science Forum 924, pp. 649-652, Published: 2018
DOI: 10.4028/www.scientific.net/MSF.924.649

16. On the Optimum Determination and Use of SiC VJFET Threshold Voltage

M. Kayambaki, N. Makris, A. Stavrinidis, G. Konstantinidis, G. Zekentes
Materials Science Forum 924, pp. 657-660, Published: 2018
DOI: 10.4028/www.scientific.net/MSF.924.65

17. Channel width effect on the operation of 4H-SiC vertical JFETs

K. Vamvoukakis, D. Stefanakis, S. Stavrinidis, K. Vassilevski, G. Konstantinidis, M. Kayambaki, K. Zekentes
PHYSICA STATUS SOLIDI A-APPLICATIONS AND MATERIALS SCIENCE, Volume: 214, Issue: 4, Article Number: 1600452, Published: APR 2017
DOI: 10.1002/pssa.201600452

18. Electrical properties of SiNx films with embedded CNTs for MEMS capacitive switches

M. Koutsourelis, G. Stavrinidis, D. Birpilotis, G. Konstantinidis, G. Papaioannou
MICROELECTRONICS RELIABILITY, Volume: 76, pp: 614-618, Special Issue: SI, Published: SEP 2017
DOI: 10.1016/j.microrel.2017.07.041

19. GaN Membrane Supported SAW Pressure Sensors with Embedded Temperature Sensing Capability

Al. Muller, G. Konstantinidis, I. Giancu, GC. Adam, A. Stefanescu, G. Stavriniadis, A. Kostopoulos, G. Boldeiu, A. Dinescu

IEEE SENSORS JOURNAL, Volume: 17, Issue: 22, pp: 7383-7393, Published: NOV 15 2017

DOI: 10.1109/JSEN.2017.2757770

20. Investigation of thin InN/GaN heterostructures with in situ SiNx dielectric grown by plasma-assisted molecular beam epitaxy

C. Zervos, A. Adikimenakis, P. Beleniotis, A. Kostopoulos, M. Androulidaki, K. Tsagaraki, M. Kayambaki, G. Konstantinidis, A. Georgakilas

Journal of Vacuum Science & Technology B, Nanotechnology and Microelectronics: Materials, Processing, Measurement, and Phenomena vol 35, 2, pp 021210, Published: 2017

DOI: 10.1116/1.4977606

21. Response to comments on "GaN/Si based single SAW resonator temperature sensor operating in the GHz frequency range"

Müller, A. Stefanescu, G. Konstantinidis

Sensors and Actuators A: Physical, vol 247, pp. 162–163, Published: 2016

DOI: 10.1016/j.sna.2016.05.047

22. A computational platform for continuous seizure anticipation, monitoring and clinical evaluation

Giannakakis, G, Padiaditis, M, Stavriniadis, G. Konstantinidis, G. Kritsotakis, V. Tsakanikas, V. Ligerakis, M. Sakkalis, V. Vorgia, M. Tsiknakis

Studies in Health technology and informatics Vol. 224, 108, Published: 2016

DOI: 10.3233/978-1-61499-653-8-108

23. Study of the effect of the operating frequency of a GaN Lamb wave device to viscosity and protein sensing

A. Pantazis, G. Konstantinidis, E. Gizeli,

IEEE sensors Journal Vol.16, No.19, 7028, Published: 2016

DOI: 10.1109/JSEN.2016.2596904

24. Enhanced Stark tuning of single InAs (211) B quantum dots due to nonlinear piezoelectric effect in zinc-blende nanostructures

S. Germanis, C. Katsidis, S. Tsintzos, A. Stavriniadis, G. Konstantinidis, N. Florini, J. Kioseoglou, G.P. Dimitrakopoulos, Th. Kehagias, Z. Hatzopoulos, N.T. Pelekanos

Physical Review Applied 6, 014004, Published: 2016

DOI: 10.1103/PhysRevApplied.6.014004

25. Selective area growth of GaN nanowires on SiO₂ masked Si (111) substrates

J. Kruse, L. Lymberakis, S. Eftychis, A. Adikimenakis, G. Doundoulakis, K. Tsagaraki, M. Androulidaki, A. Oziersky, P. Dimitrakis, V. Ioannou-Sougleridis, P. Normand, T. Koukoula, P. Komninou, G. Konstantinidis, A. Georgakilas

Journal of Applied Physics 119, 224305, Published: 2016

DOI: 10.1063/1.4953594

26. In situ SiNx/InN structures for InN field-effect transistors

C. Zervos, A. Adikimenakis, P. Beleniotis, A. Kostopoulos, M. Kayambaki, K. Tsagaraki, G. Konstantinidis, A. Georgakilas.

Applied Physics Letters 108, 142102, Published: 2016

DOI: 10.1063/1.4945668

27. Technology of integrated self-aligned E/D-mode n++GaN/InAlN/AlN/GaN MOS HEMTs for mixed signal electronics

Blaho M., Gregusova D., Hascik S., Seifertova A., Tapajna M., Soltys J., Satka A., Nagy L., Chvala A., Carlin J-f., Grandjean N., Konstantinidis G., Kuzmik J
Semiconductor Science and Technology 31, 06501, Published: 2016
DOI: 10.1088/0268-1242/31/6/065011

28. SU8 microneedles based dry electrodes for electroencephalogram

G. Stavrinidis, K. Michelakis, V. Kontomitrou, G. Giannakakis, M. Sevrisianos, G. Sevrisianos, N. Chaniotakis, Y. Alifragis, G. Konstantinidis
Microelectronic Engineering 159, 114-120, Published: 2016
DOI: 10.1016/j.mee.2016.02.062

29. Analysis of current instabilities of thin AlN/GaN/AlN double heterostructure high electron mobility transistors

Zervos, C., Adikimenakis, A., Bairamis, A., Kostopoulos, A., Kayambaki, M., Tsagaraki, K., Konstantinidis, G., Georgakilas, A.
Semiconductor Science and Technology 31, 065002, Published: 2016
DOI: 10.1088/0268-1242/31/6/065002

30. Free-Standing Gallium Nitride Membrane-Based Sensor for the Impedimetric Detection of Alcohols

Y. Alifragis, G. Roussos, A. Pantazis, G. Konstantinidis, N. Chaniotakis
Journal of Applied Physics 119, 074502, Published: 2016
DOI: 10.1063/1.4941783

31. Influence of Au based metallization on the phase velocity of GaN on Si Surface Acoustic Wave resonators

Stefanescu A., Müller A., Giangu I., Dinescu A., Konstantinidis G.
IEEE Electron Device Letters, Published: 2016
DOI: 10.1109/LED.2016.2521431

32. A tunable microwave slot antenna based on graphene

Dragoman M., Neculoiu D., Bunea A., Deligeorgis G., Aldrigo M., Vasilache D., Dinescu A., Konstantinidis G., Mencarelli D., Pierantoni L., Mondreanu M.
Applied Physics Letters Volume: 106 Issue: 15 Published: APR 13 2015
DOI: 10.1063/1.4917564

33. Sezawa Propagation Mode in GaN on Si Surface Acoustic Wave Type Temperature Sensor Structures Operating at GHz Frequencies

Mueller A., Giangu I., Stavrinidis A., Stefanescu A., Stavrinidis G., Dinescu A. Konstantinidis G.
IEEE Electron Device Letters Volume: 36 Issue: 12 Pages: 1299-1302 Published: DEC 2015
DOI: 10.1109/LED.2015.2494363

34. Characterization of a GaN Lamb-Wave Sensor for Liquid-Based Mass Sensing Applications

Pantazis A., Konstantinidis G., Gizeli E.
IEEE Sensors Journal Volume: 14 Issue: 3 Pages: 908-911 Published: MAR 2014
DOI: 10.1109/JSEN.2013.2291393

35. Comparative study of AlN dielectric films' electrical properties for MEMS capacitive switches

Koutsourelis M., Adikimenakis A., Michalas L., Papandreou E., Stavrinidis G., Konstantinidis G., Georgakilas A., Papaioannou G.
Microelectronic Engineering Volume: 130 Pages: 69-73 Published: NOV 2014
DOI: 10.1016/j.mee.2014.06.022

36. Electron density and currents of AlN/GaN high electron mobility transistors with thin GaN/AlN buffer layer

Bairamis A., Zervos Ch., Adikimenakis A., Kostopoulos A., Kayambaki M., Tsagaraki K., Konstantinidis G., Georgakilas A.

37. GaN/Si based single SAW resonator temperature sensor operating in the GHz frequency range

Mueller A., Konstantinidis G., Buiculescu V., Dinescu A., Stavrinidis A., Stefanescu A., Stavrinidis G., Giangua I., Cismaru A., Modoveanu A.

Sensors and Actuators a-Physical Volume: 209 Pages: 115-123 Published: MAR 2014

DOI: 10.1016/j.sna.2014.01.028

38. Quantum coherence in momentum space of light-matter condensates

C. Anton, G. Tosi, M. D. Martin, Z. Hatzopoulos, G. Konstantinidis, P. S. Eldridge, P. G. Savvidis, C. Tejedor, L. Vina

Physical Review B Volume: 90 Issue: 8 Published: AUG 25 2014

DOI: 10.1103/PhysRevB.90.081407

39. Electrically controlled strong coupling and polariton bistability in double quantum wells

C. Coulson, G. Christmann, P. Cristofolini, C. Grossmann, J. J. Baumberg, S. I. Tsintzos, G. Konstantinidis, Z. Hatzopoulos, P. G. Savvidis

Physical Review B Volume: 87 Issue: 4 Published: JAN 2013

DOI: 10.1103/PhysRevB.87.045311

40. Enhancement of higher harmonics in graphene-based coupled coplanar line microwave multipliers

M. Dragoman, A. Cismaru, A. Dinescu, D. Dragoman, G. Stavrinidis, G. Konstantinidis

Journal of Applied Physics Volume: 114 Issue: 15 Published: OCT 2013

DOI: 10.1063/1.4825133

41. Recombination dynamics in piezoelectric (2 1 1)B InAs quantum dots

S. Germanis, A. Beveratos, K. Gauthron, A. Stavrinidis, G. Konstantinidis, Z. Hatzopoulos, N.T. Pelekanos

Microelectronic Engineering Volume: 112 Pages: 179-182 Published: DEC 2013

DOI: 10.1016/j.mee.2013.03.159

42. Residual stress distribution and deflection analysis of very thin GaN membrane supported devices

A. Cismaru, A. Müller, G. Konstantinidis, F. Comanescu, M. Purica, A. Stefanescu, A. Stavrinidis, A. Dinescu, A. Moldoveanu

Journal of Micromechanics and Microengineering Volume: 23 Issue: 1 Published: JAN 2013

DOI: 10.1088/0960-1317/23/1/015010

43. Coupling Quantum Tunneling with Cavity Photons

P. Cristofolini, G. Christmann, S. I. Tsintzos, G. Deligeorgis, G. Konstantinidis, Z. Hatzopoulos, P. G. Savvidis, J. J. Baumberg

Science Volume: 336 Issue: 6082 Pages: 704-707 Published: MAY 11 2012

DOI: 10.1126/science.1219010

44. Effect of boiling aqua regia on MOCVD and MBE p-type GaN surfaces and Cr/p-GaN interfaces

F.G. Kalaitzakis, G. Konstantinidis, L. Sygellou, S. Kennou, S. Ladas, N.T. Pelekanos

Microelectronic Engineering Volume: 90 Pages: 115-117 Published: FEB 2012

DOI: 10.1016/j.mee.2011.04.066

45. Fabrication issues of 4H-SiC Static Induction Transistors

A. Stavrinidis, G. Konstantinidis, M. Kayambaki, F. Cayrel, D. Alquier, Z. Gao, K. Zekentes

Silicon Carbide and Related Materials 2011, Pts 1 and 2 Volume: 717-720 Pages: 1049-1052 Published: 2012

DOI: 10.4028/www.scientific.net/MSF.717-720.1049

46. Flexible chiral metamaterials in the terahertz regime: a comparative study of various designs

G. Kenanakis, R. Zhao, A. Stavrinidis, G. Konstantinidis, N. Katsarakis, M. Kafesaki, C. M. Soukoulis, E. N. Economou.

Optical Materials Express Volume: 2 Issue: 12 Pages: 1702-1712 Published: DEC 2012

DOI: <https://doi.org/10.1364/OME.2.001702>

47. Front and backside-illuminated GaN/Si based metal-semiconductor-metal ultraviolet photodetectors manufactured using micromachining and nano-lithographic technologies

A. Müller, G. Konstantinidis, M. Androulidaki, A. Dinescu, A. Stefanescu, A. Cismaru, D. Neculoiu, E. Pavelescu, A. Stavriniadis

Thin Solid Films Volume: 520 Issue: 6 Pages: 2158-2161 Published: JAN 2012

DOI: [10.1016/j.tsf.2011.09.045](https://doi.org/10.1016/j.tsf.2011.09.045)

48. Graphene radio: Detecting radiowaves with a single atom sheet

M. Dragoman, D. Neculoiu, A. Cismaru, G. Deligeorgis, G. Konstantinidis, D. Dragoman

Applied Physics Letters Volume: 101 Issue: 3 Published: JUL 2012

DOI: [10.1063/1.4738762](https://doi.org/10.1063/1.4738762)

49. Graphene-like metal-on-silicon field-effect transistor

M. Dragoman, G. Konstantinidis, K. Tsagaraki, T. Kostopoulos, D. Dragoman, D. Neculoiu

Nanotechnology Volume: 23 Issue: 30 Published: AUG 3 2012

DOI: [10.1088/0957-4484/23/30/305201](https://doi.org/10.1088/0957-4484/23/30/305201)

50. Millimeterwave Schottky diode on graphene monolayer via asymmetric metal contacts

M. Dragoman, G. Deligeorgis, A. Muller, A. Cismaru, D. Neculoiu, G. Konstantinidis, D. Dragoman, A. Dinescu, F. Comanescu

Journal of Applied Physics Volume: 112 Issue: 8 Published: OCT 2012

DOI: [10.1063/1.4759347](https://doi.org/10.1063/1.4759347)

51. Monolithic integration of nitride-based transistor with Light Emitting Diode for sensing applications

F.G. Kalaitzakis, E. Iliopoulos, G. Konstantinidis, N.T. Pelekanos

Microelectronic Engineering Volume: 90 Pages: 33-36 Published: FEB 2012

DOI: [10.1016/j.mee.2011.04.067](https://doi.org/10.1016/j.mee.2011.04.067)

52. Radio frequency signal detection by ballistic transport in Y-shaped graphene nanoribbons

G. Deligeorgis, F. Coccetti, G. Konstantinidis, R. Plana

Applied Physics Letters Volume: 101 Issue: 1 Published: JUL 2012

DOI: [10.1063/1.4732792](https://doi.org/10.1063/1.4732792)

53. Self-powered microwave devices based on graphene ink decorated with gold nanoislands

A. Radoi, M. Dragoman, A. Cismaru, G. Konstantinidis, D. Dragoman

Journal of Applied Physics Volume: 112 Issue: 6 Published: SEP 15 2012

DOI: [10.1063/1.4754860](https://doi.org/10.1063/1.4754860)

54. Analysis of GaN Based SAW Resonators including FEM Modeling

Stefanescu, A., Neculoiu, D., Mueller, A., A. Dinescu., G. Konstantinidis., A. Stavriniadis

Romanian Journal of Information Science and Technology Volume: 14 Issue: 4 Pages: 334-345 Published: 2011

ISSN: 1453-8245

55. Coplanar waveguide on graphene in the range 40 MHz-110 GHz

M. Dragoman, D. Neculoiu, A. Cismaru, A. Muller, G. Deligeorgis, G. Konstantinidis, D. Dragoman, R. Plana

Applied Physics Letters Volume: 99 Issue: 3 Published: JUL 2011

DOI: [10.1063/1.3615289](https://doi.org/10.1063/1.3615289)

56. Electrical behavior of multi-walled carbon nanotube network embedded in amorphous silicon nitride

I. Stavarache, A. M. Lepadatu, V. S. Teodorescu, M. L. Ciurea, V. Iancu, M. Dragoman, G. Konstantinidis, R. Buiculescu

Nanoscale Research Letters Volume: 6 Published: 2011

DOI: [10.1186/1556-276X-6-88](https://doi.org/10.1186/1556-276X-6-88)

57. A high frequency GaN Lamb-wave sensor device

Pantazis, A., Gizeli, E., Konstantinidis, G.

Applied Physics Letters Volume: 96 Issue: 19 Published: MAY 10 2010

DOI: 10.1063/1.3427484

58. Graphene for Microwaves

M. Dragoman, D. Neculoiu, D. Dragoman, G. Deligeorgis, G. Konstantinidis, A. Cismaru, F. Coccetti, R. Plana

IEEE Microwave Magazine Volume: 11 Issue: 7 Pages: 81-86 Published: DEC 2010

DOI: 10.1109/MMM.2010.938568

59. Interfacial polarisation on gallium arsenide membranes

T. Prodromakis, G. Konstantinidis, C. Papavassiliou, C. Toumazou

Micro & Nano Letters Volume: 5 Issue: 3 Pages: 178-180 Published: JUN 2010

DOI: 10.1049/mnl.2010.0008

60. MEMS Switch for 60 GHz Band

D. Vasilache, G. Konstantinidis, M. Dragoman, A. Takacs, F. Vladoianu, T. Kostopoulos, G. Boldeiu, V. Moagar, C. Tibeica, L. Bary, R. Plana, P. Schiopu, G. Caruntu

Advanced Topics in Optoelectronics, Microelectronics, and Nanotechnologies V Volume: 7821
Published: 2010

DOI: 10.1117/12.881775

61. Microwave and millimeter wave devices based on micromachining of III-V semiconductors

A. Müller, D. Neculoiu, G. Konstantinidis, T. Vähä-heikilä

Advanced Materials and Technologies for Micro/nano-Devices, Sensors and Actuators Pages: 75-87
Published: 2010

DOI: 10.1007/978-90-481-3807-4_6

62. Microwave switching of graphene field effect transistor at and far from the Dirac point

G. Deligeorgis, M. Dragoman, D. Neculoiu, D. Dragoman, G. Konstantinidis, A. Cismaru, R. Plana

Applied Physics Letters Volume: 96 Issue: 10 Published: MAR 2010

DOI: 10.1063/1.3358124

63. Millimeter-wave generation via frequency multiplication in graphene

M. Dragoman, D. Neculoiu, G. Deligeorgis, G. Konstantinidis, D. Dragoman, A. Cismaru, A. A. Muller, R. Plana

Applied Physics Letters Volume: 97 Issue: 9 Published: AUG 2010

DOI: 10.1063/1.3483872

64. Negative differential resistance in GaN nanowire network

M. Dragoman, G. Konstantinidis, A. Cismaru, D. Vasilache, A. Dinescu, D. Dragoman, D. Neculoiu, R. Buiculescu, G. Deligeorgis, A. P. Vajpeyi, A. Georgakilas

Applied Physics Letters Volume: 96 Issue: 5 Published: FEB 2010

DOI: 10.1063/1.3309670

65. SAW Devices Manufactured on GaN/Si for Frequencies Beyond 5 GHz

A. Mueller, D. Neculoiu, G. Konstantinidis, G. Deligeorgis, A. Dinescu, A. Stavrinidis, A. Cismaru, M. Dragoman, A. Stefanescu.

IEEE Electron Device Letters Volume: 31 Issue: 12 Pages: 1398-1400 Published: DEC 2010

DOI: 10.1109/LED.2010.2078484

66. 6.3-GHz Film Bulk Acoustic Resonator Structures Based on a Gallium Nitride/Silicon Thin Membrane

A. Muller, D. Neculoiu, G. Konstantinidis, A. Stavrinidis, D. Vasilache, A. Cismaru, M. Danila, M. Dragoman, G. Deligeorgis, K. Tsagaraki

IEEE Electron Device Letters Volume: 30 Issue: 8 Pages: 799-801 Published: AUG 2009

DOI: 10.1109/LED.2009.2023538

67. AlN on silicon-based surface acoustic wave resonators operating at 5 GHz

D. Neculoiu, A. Muller, G. Deligeorgis, A. Dinescu, A. Stavrinidis, D. Vasilache, A.M. Cismaru, G.E. Stan, G. Konstantinidis

Electronics Letters Volume: 45 Issue: 23 Pages: 1196-1197 Published: NOV 5 2009

DOI: 10.1049/el.2009.2520

68. Application of gold nanodots for Maxwell-Wagner loss reduction

T. Prodromakis, C. Papavassiliou, G. Konstantinidis, C. Toumazou

Micro & Nano Letters Volume: 4 Issue: 2 Pages: 80-83 Published: JUN 2009

DOI: 10.1049/mnl.2009.0016

69. Current oscillations in a wide graphene sheet

M. Dragoman, D. Dragoman, G. Deligiorgis, G. Konstantinidis, D. Neculoiu, A. Cismaru, R. Plana

Journal of Applied Physics Volume: 106 Issue: 4 Published: AUG 15 2009

DOI: 10.1063/1.3208061

70. Fabrication and Characterization of Cr-based Schottky Diode on n-type 4H-SiC

C. Koliakoudakis, J. Dontas, S. Karakalos, M. Kayambaki, S. Ladas, G. Konstantinidis, S. Kennou, K. Zekentes

Silicon Carbide and Related Materials 2008 Volume: 615-617 Pages: 651-654 Published: 2009

DOI: 10.4028/www.scientific.net/MSF.615-617.651

71. GaN membrane-supported UV photodetectors manufactured using nanolithographic processes

A. Müller, G. Konstantinidis, M. Dragoman, D. Neculoiu, A. Dinescu, M. Androulidaki, M. Kayambaki, A. Stavrinidis, D. Vasilache, C. Buiculescu, I. Petrini, A. Kostopoulos, D. Dascalu.

Microelectronics Journal Volume: 40 Issue: 2 Pages: 319-321 Published: FEB 2009

DOI: 10.1016/j.mejo.2008.07.021

72. High electron mobility transistors based on the AlN/GaN heterojunction

A. Adikimenakis, K.E. Aretouli, E. Iliopoulos, A. Kostopoulos, K. Tsagaraki, G. Konstantinidis, A. Georgakilas

DOI: 10.1016/j.mee.2009.02.004

73. InAs nanostructures on polar GaAs surfaces

G.E. Dialynas, A. Pantazis, Z. Hatzopoulos, M. Androulidaki, K. Tsagaraki, G. Konstantinidis, C. Xenogianni, E. Trichas, S. Tsintzos, P.G. Savvidis, N.T. Pelekanos

International Journal of Nanotechnology Volume: 6 Issue: 1-2 Pages: 124-136 Published: 2009

DOI: 10.1504/IJNT.2009.021712

74. Microwave propagation in graphene

G. Deligeorgis, M. Dragoman, D. Neculoiu, D. Dragoman, G. Konstantinidis, A. Cismaru, R. Plana

Applied Physics Letters Volume: 95 Issue: 7 Published: AUG 17 2009

DOI: 10.1063/1.3202413

75. Rapid thermal annealing temperature dependence of noise properties in Au/n-GaAs Schottky diodes with embedded InAs quantum dots in asymmetric In_{0.2}Ga_{0.8}As wells

N. Arpatzanis, N. A. Hastas, C. A. Dimitriadis, G. Konstantinidis, C. Charitidis, J. D. Song, W. J. Choi, J. I. Lee

Physica Status Solidi B-Basic Solid-State Physics Volume: 246 Issue: 4 Pages: 880-884 Published: APR 2009

DOI: 10.1002/pssb.200880580

76. A GaAs polariton light-emitting diode operating near room temperature

S. I. Tsintzos, N. T. Pelekanos, G. Konstantinidis, Z. Hatzopoulos, P. G. Savvidis

Nature Volume: 453 Issue: 7193 Pages: 372-375 Published: MAY 15 2008

DOI: 10.1038/nature06979

77. Anti-binding of biexcitons in (211) B InAs/GaAs piezoelectric quantum dots

G.E. Dialynas, C. Xenogianni, S. Tsintzos, E. Trichas, P.G. Savvidis, G. Konstantinidis, J. Renard, B. Gayral, Z. Hatzopoulos, N.T. Pelekanos

Physica E-Low-Dimensional Systems & Nanostructures Volume: 40 Issue: 6 Pages: 2113-2115 Published: APR 2008

DOI: 10.1016/j.physe.2007.10.036

78. Cr/4H-SiC Schottky contacts investigated by electrical and photoelectron spectroscopy techniques

C. Koliakoudakis¹, J. Dontas, S. Karakalos, M. Kayambaki, S. Ladas, G. Konstantinidis, K. Zekentes, S. Kennou

Physica Status Solidi a-Applications and Materials Science Volume: 205 Issue: 11 Pages: 2536-2540 Published: NOV 2008

DOI: 10.1002/pssa.200780212

79. Dielectric charging effect estimation to MIM structured RF MEMS devices due to 1 MeV gamma-ray photons irradiation

V. Theonas, G. Papaioannou, G. Konstantinidis, J. Papapolumerou

Physica Status Solidi C - Current Topics in Solid State Physics, Vol 5, No 12 2008 Volume: 5 Issue: 12 Pages: 3850-3853 Published: 2008

DOI: 10.1002/pssc.200780186

80. Estimation of metallic contact effects on the performance of (SI) GaAs soft X-ray radiation detectors

V. Theonas, G. Papaioannou, G. Konstantinidis, J. Papapolumerou

Physica Status Solidi C - Current Topics in Solid State Physics, Vol 5, No 12 2008 Volume: 5 Issue: 12 Pages: 3638-3642 Published: 2008

DOI: 10.1002/pssc.200780216

81. GaN membrane metal-semiconductor-metal ultraviolet photodetector

A. Müller, G. Konstantinidis, M. Dragoman, D. Neculoiu, A. Kostopoulos, M. Androulidaki, M. Kayambaki, D. Vasilache.

Applied Optics Volume: 47 Issue: 10 Pages: 1453-1456 Published: APR 2008

DOI: 10.1364/AO.47.001453

82. Metallic bonding methodology for heterogeneous integration of optoelectronic dies to CMOS circuits

P. Robogiannakis, E.D. Kyriakis-Bitzaros, K. Minoglou, S. Katsafouros, A. Kostopoulos, G. Konstantinidis, G. Halkias

Microelectronic Engineering Volume: 85 Issue: 4 Pages: 727-732 Published: APR 2008

DOI: 10.1016/j.mee.2008.01.053

83. Millimeter-Wave Identification-A New Short-Range Radio System for Low-Power High Data-Rate Applications

Pursula, P., Vaha-Heikkila, T., Muller, A., Neculoiu, D., Konstantinidis G., Oja, A., Tuovinen, J.

IEEE Transactions on Microwave Theory and Techniques Volume: 56 Issue: 10 Pages: 2221-2228 Published: OCT 2008

DOI: 10.1109/TMTT.2008.2004252

84. Multiple negative resistances in trenched structures bridged with carbon nanotubes

M. Dragoman, G. Konstantinidis, A. Kostopoulos, D. Dragoman, D. Neculoiu, R. Buiculescu, R. Plana, F. Coccetti, H. Hartnagel

Applied Physics Letters Volume: 93 Issue: 4 Published: JUL 2008

DOI: 10.1063/1.2963367

85. Negative index short-slab pair and continuous wires metamaterials in the far infrared regime

T. F. Gundogdu, N. Katsarakis, M. Kafesaki, R. S. Penciu, G. Konstantinidis, A. Kostopoulos, E. N. Economou, C. M. Soukoulis

Optics Express Volume: 16 Issue: 12 Pages: 9173-9180 Published: JUN 2008

DOI: 10.1364/OE.16.009173

86. Towards electrically-pumped microcavity polariton lasers

S. Tsintzos, P. G. Savvidis, G. Konstantinidis, Z. Hatzopoulos, N. T. Pelekanos

Physica Status Solidi C - Current Topics in Solid State Physics, Vol 5, No 12 2008 Volume: 5 Issue: 12 Pages: 3594-3596 Published: 2008

DOI: 10.1002/pssc.200780210

87. AlGa_N/Ga_N high electron mobility transistor sensor sensitive to ammonium ions

Y. Alifragis, A. Volosirakis, N. A. Chaniotakis, G. Konstantinidis, E. Iliopoulos, A. Georgakilas

Physica Status Solidi a-Applications and Materials Science Volume: 204 Issue: 6 Pages: 2059-2063 Published: JUN 2007

DOI: 10.1002/pssa.200674885

88. Gate-lag and drain-lag effects in (Ga_N)/InAlN/Ga_N and InAlN/AlN/Ga_N HEMTs

J. Kuzmik, J.-F. Carlin, M. Gonschorek, A. Kostopoulos, G. Konstantinidis, G. Pozzovivo, S. Golka, A. Georgakilas, N. Grandjean, G. Strasser, D. Pogany

Physica Status Solidi a-Applications and Materials Science Volume: 204 Issue: 6 Pages: 2019-2022 Published: JUN 2007

DOI: 10.1002/pssa.200674707

89. Growth optimization of an electron confining InN/Ga_N quantum well heterostructure

E. Dimakis, E. Iliopoulos, M. Kayambaki, K. Tsagaraki, A. Kostopoulos, G. Konstantinidis, A. Georgakilas

Journal of Electronic Materials Volume: 36 Issue: 4 Pages: 373-378 Published: APR 2007

DOI: 10.1007/s11664-006-0041-0

90. Low resistance as-deposited Cr/Au contacts on p-type Ga_N

Kalaitzakis, F. G., Pelekanos, N. T., Prystawko, P., Leszczynski, M., Konstantinidis, G.

Applied Physics Letters Volume: 91 Issue: 26 Published: DEC 2007

DOI: 10.1063/1.2828044

91. Potassium selective chemically modified field effect transistors based on AlGa_N/Ga_N two-dimensional electron gas heterostructures

Y. Alifragisa, A. Volosirakis, N.A. Chaniotakis, G. Konstantinidis, A. Adikimenakis, A. Georgakilas

Biosensors & Bioelectronics Volume: 22 Issue: 12 Pages: 2796-2801 Published: JUN 15 2007

DOI: 10.1016/j.bios.2006.10.010

92. Effect of space charge polarization in radio frequency microelectromechanical system capacitive switch dielectric charging

G. J. Papaioannou, M. Exarchos, V. Theonas, J. Psychias, G. Konstantinidis, D. Vasilache, A. Muller, D. Neculoiu

Applied Physics Letters Volume: 89 Issue: 10 Published: SEP 2006

DOI: 10.1063/1.2347278

93. Experimental demonstration of negative magnetic permeability in the far-infrared frequency regime

T. F. Gundogdu, I. Tsiapa, A. Kostopoulos, G. Konstantinidis, N. Katsarakis, R. S. Penciu, M. Kafesaki, E. N. Economou, Th. Koschny, C. M. Soukoulis

Applied Physics Letters Volume: 89 Issue: 8 Published: AUG 2006

DOI: 10.1063/1.2335955

94. Ga_N micromachined FBAR structures for microwave applications

Müller, A., Neculoiu, D., Vasilache, D., Dascalu, D., Konstantinidis, G., Kosopoulos, A., Adikimenakis, A., Georgakilas, A., Mutamba, K., Sydlo, C., Hartnagel, H. L., Dadgar, A.

Superlattices and Microstructures Volume: 40 Issue: 4-6 Pages: 426-431 Published: OCT-DEC 2006

DOI: 10.1016/j.spmi.2006.07.014

95. High performance thin film bulk acoustic resonator covered with carbon nanotubes

M. Dragoman, A. Muller, D. Neculoiu, D. Vasilache, G. Konstantinidis, K. Grenier, D. Dubuc, L.

Bary, R. Plana, E. Flahaut

Applied Physics Letters Volume: 89 Issue: 14 Published: OCT 2006

DOI: 10.1063/1.2358838

96. InAlN/GaN HEMTs: A first insight into technological optimization
Kuzmik, J, Kostopoulos, A., Konstantinidis, G. Carlin, J.-F. , Georgakilas, A., Pogany, D.
IEEE Transactions on Electron Devices Volume: 53 Issue: 3 Pages: 422-426 Published: MAR 2006
DOI: 10.1109/TED.2005.864379

97. Optical cavity formation on GaN using a conventional RIE system

F. G. Kalaitzakis, G. Konstantinidis, K. Tsagaraki, M. Androulidaki, N. T. Pelekanos
Physica Status Solidi C - Current Topics in Solid State Physics, Vol 3, No 6 Volume: 3 Issue: 6 Pages: 1798-1802, Published: 2006
DOI: 10.1002/pssc.200565281

98. RF MEMS dielectric sensitivity to electromagnetic radiation

Theonas, V. T. Exarchos, M., Papaioannou, G. J., Konstantinidis, G.
Sensors and Actuators a-Physical Volume: 132 Issue: 1 Pages: 25-33 Published: NOV 8 2006
DOI: 10.1016/j.sna.2006.06.020

99. Via hole formation in silicon carbide by laser micromachining

K. Zekentes, I. Zergioti, A. Klini, G. Konstantinidis
Silicon Carbide and Related Materials 2005, Pts 1 and 2 Volume: 527-529 Pages: 1119-1121 Published: 2006
DOI: 10.4028/www.scientific.net/MSF.527-529.1119

100. Active nitrogen species dependence on radiofrequency plasma source operating parameters and their role in GaN growth

E. Iliopoulos, A. Adikimenakis, E. Dimakis, K. Tsagaraki, G. Konstantinidis, A. Georgakilas
Journal of Crystal Growth Volume: 278 Issue: 1-4 Pages: 426-430 Published: MAY 2005
DOI: 10.1016/j.jcrysgro.2005.01.013

101. Anion selective potentiometric sensor based on gallium nitride crystalline membrane

Y. Alifragis, G. Konstantinidis, A. Georgakilas, N. Chaniotakis
Electroanalysis Volume: 17 Issue: 5-6 Pages: 527-531 Published: MAR 2005
DOI: 10.1002/elan.200403191

102. GaN-based anion selective sensor: Probing the origin of the induced electrochemical potential

N. A. Chaniotakis, Y. Alifragis, A. Georgakilas, G. Konstantinidis
Applied Physics Letters Volume: 86 Issue: 16 Published: APR 2005
DOI: 10.1063/1.1896449

103. Magnetic response of split-ring resonators in the far-infrared frequency regime

N. Katsarakis, G. Konstantinidis, A. Kostopoulos, R. S. Penciu, T. F. Gundogdu, M. Kafesaki, E. N. Economou, Th. Koschny, and C. M. Soukoulis
Optics Letters Volume: 30 Issue: 11 Pages: 1348-1350 Published: JUN 2005
DOI: 10.1364/OL.30.001348

104. Millimeter-wave passive circuit elements based on GaAs micromachining

A. Pantazis, D. Neculoiu, Z. Hatzopoulos, D. Vasilache, M. Lagadas, M. Dragoman, C. Buiculescu, I. Petrini, A. A. Müller, G. Konstantinidis
Journal of Micromechanics and Microengineering Volume: 15 Issue: 7 Pages: S53-S59 Published: JUL 2005
DOI: 10.1088/0960-1317/15/7/008

105. Response to anions of AlGaIn/GaN high-electron-mobility transistors

Alifragis, Y., Georgakilas, A., Konstantinidis, G., Iliopoulos, E., Kostopoulos, A., Chaniotakis N.A
Applied Physics Letters Volume: 87 Issue: 25 Published: DEC 19 2005
DOI: 10.1063/1.2149992

106. Temperature dependence of GaN Schottky diodes I-V characteristics

J. Osvald, J. Kuzmik, G. Konstantinidis, P. Lobotka, A. Georgakilas
Microelectronic Engineering Volume: 81 Issue: 2-4 Pages: 181-187 Published: AUG 2005

107. Gallium nitride-based potentiometric anion sensor

N. A. Chaniotakis, Y. Alifragis, G. Konstantinidis, A. Georgakilas
Analytical Chemistry Volume: 76 Issue: 18 Pages: 5552-5556 Published: SEP 2004
DOI: 10.1021/aco49476h

108. The role of nucleation temperature in In-face InN-on-GaN(0001) growth by plasma assisted molecular beam epitaxy

E. Dimakis, G. Konstantinidis, K. Tsagaraki, A. Adikimenakis, E. Iliopoulos, A. Georgakilas
Superlattices and Microstructures Volume: 36 Issue: 4-6 Pages: 497-507 Published: OCT-DEC 2004
DOI: 10.1016/j.spmi.2004.09.010

109. ZrO₂/(Al)GaN metal-oxide-semiconductor structures: characterization and application

J. Kuzmík, G. Konstantinidis, S. Harasek, Š. Haščík, E. Bertagnolli, A. Georgakilas, D. Pogany
Semiconductor Science and Technology Volume: 19 Issue: 12 Pages: 1364-1368 Published: DEC 2004
DOI: 10.1088/0268-1242/19/12/006

110. Field-compensated quaternary InAlGa_n/Ga_n quantum wells

F. Kalaitzakis, M. Androulidaki, N. T. Pelekanos, E. Dimakis, E. Bellet-Amalric, D. Jalabert, D. Cengher, K. Tsagaraki, E. Aperathitis, G. Konstantinidis, A. Georgakilas
Physica Status Solidi B-Basic Research Volume: 240 Issue: 2 Pages: 301-304 Published: NOV 2003
DOI: 10.1002/pssb.200303536

111. GaAs membrane supported millimeter-wave receiver structures

G Konstantinidis, D Neculoiu, M Lagadas, G Deligeorgis, D Vasilache, A Muller
Journal of Micromechanics and Microengineering Volume: 13 Issue: 3 Pages: 353-358 Published: MAY 2003
DOI: 10.1088/0960-1317/13/3/301

112. Role of As precipitates on ultrafast electron trapping in low-temperature grown GaAs and AlGaAs alloys

Loukakos T, Kalpouzou C., Hatzopoulos Z., Sfendourakis M., Konstantinidis G., Fotakis C
Journal of Applied Physics Volume: 91 Issue: 12 Pages: 9863-9868 Published: JUNE 2002
DOI: 10.1063/1.1477614

113. Investigation into the charge distribution and barrier profile tailoring in AlGa_n/Ga_n double heterostructures by self-consistent Poisson-Schrodinger calculations and capacitance-voltage profiling

M. Zervos, A. Kostopoulos, G. Constantinidis, M. Kayambaki, A. Georgakilas
Journal of Applied Physics Volume: 91 Issue: 7 Pages: 4387-4393 Published: APR 2002
DOI: 10.1063/1.1459604

114. Use of laser interferometry and optical emission spectroscopy for monitoring the reactive ion etching of 6H- and 4H-SiC

Camara, N, Constantinidis, G, Zekentes, K,
Silicon Carbide and Related Materials - 2002 Volume: 433-4 Pages: 693-696 Published: 2002
DOI: 10.4028/www.scientific.net/MSF.433-436.693

115. GaAs planar doped barrier diodes

B. Szentpali, Vo Van Tuyen, G. Constantinidis, M. Lagadas
Materials Science and Engineering B-Solid State Materials for Advanced Technology Volume: 80 Issue: 1-3 Pages: 257-261 Published: MAR 22 2001
DOI: 10.1016/S0921-5107(00)00650-4

116. Micromachined filters for 38 and 77 GHz supported on thin membranes

A. Muller, G. Constantinidis, F. Giacomozzi, M. Lagadas, G. Deligeorgis, S. Iordanescu, I. Petrini, D. Vasilache, R. Marcelli, G. Bartolucci, D. Neculoiu, C. Buiculescu, P. Blondy, D. Dascalu

117. Phase formation at rapid thermal annealing of Al/Ti/Ni ohmic contacts on 4H-SiC

Vassilevski, K, Zekentes, K, Tsagaraki, K, Constantinidis G, Nikitina I,
Materials Science and Engineering B-Solid State Materials for Advanced Technology Volume: 80 Issue: 1-3
Pages: 370-373 Published: MAR 2001
DOI: 10.1016/S0921-5107(00)00597-3

118. Study of the correlation between GaN material properties and the growth conditions of radio frequency plasma-assisted molecular beam epitaxy

K. Amimer, A. Georgakilas, M. Androulidaki, K. Tsagaraki, M. Pavelescu, S. Mikroulis, G. Constantinidis, J. Arbiol, F. Peiro, A. Cornet, M. Calamiotou, J. Kuzmik, V.Y. Davydov
Materials Science and Engineering B-Solid State Materials for Advanced Technology Volume: 80 Issue: 1-3
Pages: 304-308 Published: MAR 2001
DOI: 10.1016/S0921-5107(00)00646-2

119. The pinch-off behaviour and charge distribution in AlGaIn-GaN-AlGaIn-GaN double heterostructure field effect transistors

M. Zervos, A. Kostopoulos, G. Constantinidis, M. Kayambaki, S. Mikroulis, N. Flytzanis, A. Georgakilas
Physica Status Solidi a-Applied Research Volume: 188 Issue: 1 Pages: 259-262 Published: NOV 2001
DOI: 10.1002/1521-396X(200111)188:1<259::AID-PSSA259>3.3.CO;2-X

120. Direct MBE growth of GaN on GaAs substrates for integrated short wavelength emitters

A. Georgakila, K. Tsagaraki, E. Makarona, G. Constantinidis, M. Adroulidaki, M. Kayambaki, E. Aperathitis, N.T Pelekanos
Materials Science in Semiconductor Processing Volume: 3 Issue: 5-6 Pages: 511-515 Published: OCT-DEC 2000
DOI: 10.1016/S1369-8001(00)00076-7

121. Fabrication and electrical characterization of 4H-SiC p(+)-n-n(+) diodes with low differential resistance

Vassilevski, K, Zekentes, K, Constantinidis, G, Strelchuk A.
Solid-State Electronics Volume: 44 Issue: 7 Pages: 1173-1177 Published: JUL 2000
DOI: 10.1016/S0038-1101(00)00053-8

122. Polyimide based GaAs micromachined millimeter wave structures

A. Müller, S. Iordanescu, I. Petrini, V. Avramescu, G. Simion, D. Vasilache, V. Badilita, D. Dascalu, G. Konstantinidis, R. Marcelli
Journal of Micromechanics and Microengineering Volume: 10 Issue: 2 Pages: 130-135 Published: JUN 2000
DOI: 10.1088/0960-1317/10/2/306

123. Resistive pressure sensing structures on polyimide membranes on GaAs substrate

I. Petrini, A. Müller, V. Avramescu, G. Simion, N. Nitescu, D. Vasilache, D. Dascalu, G. Konstantinidis, F. Giacomozzi
Journal of Micromechanics and Microengineering Volume: 10 Issue: 2 Pages: 218-222 Published: JUN 2000
DOI: 10.1088/0960-1317/10/2/320

124. Structural and morphological characterization of Al/Ti-based ohmic contacts on p-type 4H-SiC annealed under various conditions

Vassilevski, K. V, Zekentes, K, Constantinidis, G, Papanicolaou N. Nikitina I. P., Babanin A. I.
Silicon Carbide and Related Materials - 1999 Pts, 1 & 2 Volume: 338-3 Pages: 1017-1020 Published: 2000
DOI: 10.4028/www.scientific.net/MSF.338-342.1017

125. Improvements in Pt-based Schottky contacts to 3C-SiC

G. Constantinidis, B. Pecz, K. Tsagaraki, M. Kayambakia, K. Michelakis

Materials Science and Engineering B-Solid State Materials for Advanced Technology Volume: 61-2 Pages: 406-410 Published: JUL 1999

DOI: 10.1016/S0921-5107(98)00543-1

126. Influence of MBE growth temperature on the properties of cubic GaN grown directly on GaAs substrates

A. Georgakilas, M. Androulidaki, K. Tsagaraki, K. Amimer, G. Constantinidis, N. T. Pelekanos, M. Calamiotou, Zs. Czigany, B. Pecz

Physica Status Solidi a-Applied Research Volume: 176 Issue: 1 Pages: 525-528 Published: NOV 1999

DOI: 10.1002/(SICI)1521-396X(199911)176:1<525::AID-PSSA525>3.0.CO;2-M

127. Study of annealing conditions on the formation of ohmic contacts on p+4H-SiC layers grown by CVD and LPE

Vassilevski, KV, Constantinidis, G, Papanicolaou, N, Martin N., Zekentes K.

Materials Science and Engineering B-Solid State Materials for Advanced Technology Volume: 61-2 Pages: 296-300 Published: JUL 30 1999

DOI: 10.1016/S0921-5107(98)00521-2

128. Highly selective two-ion-carrier chemically modified FET's

Chaniotakis, NA, Moschou, EA, Constantinidis, G

Microelectronic Engineering Volume: 42 Pages: 481-483 Published: MAR 1998

DOI: [https://doi.org/10.1016/S0167-9317\(98\)00112-9](https://doi.org/10.1016/S0167-9317(98)00112-9)

129. Ion irradiation induced defects in epitaxial GaAs layers

N. Arpatzanis, R. Vlastou, G. Konstantinidis, W. Assmann, M. Papastamatiou, E. Gazis, G.J Papaioannou

Solid-State Electronics Volume: 42 Issue: 2 Pages: 277-282 Published: FEB 1998

DOI: 10.1016/S0038-1101(97)00221-9

130. Schottky contacts on CF₄/H₂ reactive ion etched beta-SiC

Constantinidis, G, Kuzmic, J, Michelakis, K, Tsagaraki K.

Solid-State Electronics Volume: 42 Issue: 2 Pages: 253-256 Published: FEB 1998

DOI: 10.1016/S0038-1101(97)00224-4

131. Diffusion of gold in 3C-SiC epitaxially grown on Si - Structural characterization

N. Kornilios, G. Constantinidis, M. Kayiambaki, K. Zekentes, J. Stoemenos

Materials Science and Engineering B-Solid State Materials for Advanced Technology Volume: 46 Issue: 1-3 Pages: 186-189 Published: APR 1997

DOI: 10.1016/S0921-5107(96)01960-5

132. Failure mechanisms of GaAs MESFETS with Cu/refractory metallized gates

T. Feng, A. Dimoulas, A. Christou, G. Constantinidis, Z. Hatzopoulos

Microelectronics and Reliability Volume: 37 Issue: 10-11 Pages: 1699-1702 Published: OCT-NOV 1997

DOI: 10.1016/S0026-2714(97)00143-1

133. High temperature ohmic contacts to 3C-SiC grown on Si substrates by chemical vapor deposition

Constantinidis G., Kornilios N., Zekentes K., Stoemenos J., L. di Cioccio

Materials Science and Engineering B-Solid State Materials for Advanced Technology Volume: 46 Issue: 1-3 Pages: 176-179 Published: APR 1997

DOI: 10.1016/S0921-5107(96)01958-7

134. Schottky contact investigation on reactive ion etched 6H alpha-SiC

Constantinidis, G, Kuzmik, J, Michelakis, K

Diamond and Related Materials Volume: 6 Issue: 10 Pages: 1459-1462 Published: AUG 1997

DOI: 10.1016/S0925-9635(97)00112-X

135. Effects of Si(100) tilting angle and prelayer conditions on GaAs/Si heterostructures

A. Georgakilas, Ch. Papavassiliou, G. Constantinidis, K. Tsagaraki, H. Krasny, E. Löchtermann, P. Panayotatos

Applied Surface Science Volume: 102 Pages: 67-72 Published: AUG 1996

136. High-temperature stable Ir-Al/n-GaAs Schottky diodes: Effect of the barrier height controlling

T. Lalinský, J. Osvald, D. Machajdík, Ž. Mozolová, J. Šišolák, G. Constantinidis, A. P. Kobzev
Journal of Vacuum Science & Technology B Volume: 14 Issue: 2 Pages: 657-661 Published: MAR-APR 1996

137. Electron traps in beta SiC grown by chemical vapour deposition on silicon (100) substrates

Zekentes, K, Kayiambaki, M, Constantinidis, G
Applied Physics Letters Volume: 66 Issue: 22 Pages: 3015-3017 Published: MAY 29 1995
DOI: 10.1063/1.114262

138. Investigation of Si-substrate preparation for GaAs-on-Si MBE growth

M. Kayambaki, R. Callea, G. Constantinidis, Ch. Papavassiliou, E. Löchtermann, H. Krasny, N. Papadakis, P. Panayotatos, A. Georgakilas
Journal of Crystal Growth Volume: 157 Issue: 1-4 Pages: 300-303 Published: DEC 1995
DOI: 10.1016/0022-0248(95)00336-3

139. A comprehensive optimization of InAlAs molecular beam epitaxy for InGaAs/InAlAs HEMT technology

A. Georgakilas, G. Halkias, A. Christou, N. Kornilios, C. Papavassiliou, K. Zekentes, G. Konstantinidis, F. Peiró, A. Cornet, S. Ababou, A. Tabata, G. Guillot
Journal of the Electrochemical Society Volume: 140 Issue: 5 Pages: 1503-1509 Published: MAY 1993
DOI: 10.1149/1.2221587

140. Microwave performance of GaAs on Si MESFETs with Si buffer layers

Georgakilas A., Halkias G., Christou A., Papavassiliou C., Perantinos G., Konstantinidis G., Panayotatos P. N
IEEE Transactions on Electron Devices Volume: 40 Issue: 3 Pages: 507-512 Published: MAR 1993
DOI: 10.1109/16.199355

141. Reactive Ion Etching of beta-SiC in CCL₂F₂/O₂

Kuzmik, J, Michelakis, C, Konstantinidis, G, Papanicolaou N.
Electronics Letters Volume: 29 Issue: 1 Pages: 18-19 Published: JAN 7 1993
DOI: 10.1049/el:19930012

142. Deep level analysis of undoped Ga_xIn_{1-x} P/GaAs single heterojunctions grown by MOMBE and MOVPE

E.C. Paloura, A. Ginoudi, G. Constantinidis, G. Kiriakidis
Sensors and Actuators a-Physical Volume: 33 Issue: 1-2 Pages: 63-66 Published: MAY 1992
DOI: 10.1016/0924-4247(92)80227-T

143. Low temperature DC characteristics of S-doped and Si-doped Ga_{0.51}In_{0.49}P/GaAs high electron mobility transistors grown by metalorganic molecular beam epitaxy

A. Ginoudi, E. C. Paloura, G. Kostandinidis, G. Kiriakidis, Ph. Maurel, J. C. Garcia, A. Christou
Applied Physics Letters Volume: 60 Issue: 25 Pages: 3162-3164 Published: JUN 22 1992
DOI: 10.1063/1.106729

144. Microhardness of CuInSe₂

Constantinidis, G., Tomlinson, R. D., Neumann, H.
Philosophical Magazine Letters Volume: 57 Issue: 2 Pages: 91-97 Published: FEB 1988
DOI: 10.1080/09500838808229616

145. The observation of near surface deviations from in CuInSe₂ crystals following chemical etching

M.V. Yakushev, G. Constantinidis, M. Imanieh, R.D. Tomlinson
Solid State Communications Volume: 65 Issue: 10 Pages: 1079-1083 Published: MAR 1988
DOI: 10.1016/0038-1098(88)90897-6

[1.3]. INVITED CHAPTERS IN BOOKS

[1]. Membrane supported millimeter wave circuits based on silicon and GaAs micromachining

Al. Müller, D. Neculoiu, G. Konstantinidis, R. Plana
in "Wireless Technologies, Circuits, Systems and Devices"
CRC Press, Taylor&Francis Group, Editor: Krzysztof Iniewski, 2007

[1.4]. CHAPTERS IN BOOKS

[2]. Review on recent developments of GaN/Si surface acoustic wave-based sensors

"Advances in micro and nanoelectronics"
Series in Micro and Nanoengineering, Publishing House of the Romanian Academy, 2018,
Editors: S. Cristoloveanu, A. Wild, D. Dascalu, ISBN 978-973-27-2982-3, pp.332-356

[3]. Open Special issue: Emerging materials and processes for nanoelectronics and sensors

Guest editors A. Georgakilas and G. Konstantinidis
Microelectronic Engineering, Volume: 112, Dec. 2013

[4]. Microwave characterization and DC measurements of CPW line based on a wide graphene sheet

A. Cismaru, M. Dragoman, G. Deligeorgis, D. Neculoiu, G. Konstantinidis, D. Dragoman, R. Plana in
"Microwave Circuits and devices based on MEMS technologies"
Series in Micro and Nanoengineering, Publishing House of the Romanian Academy, 2011,
Editors: L Tarricone, A Muller, D Dascalu, R Sorrentino, ISBN 978-973-27-2068, pp.287-294

[5]. Recent progresses in acoustic devices on GaN/Si

A. Müller, D. Neculoiu, A. Stavrinidis, T. Kostoupulos, A. Dinescu, A. Cismaru, D. Vasilache, G. Deligiorgis,
C. Buiculescu, A.A. Müller, I. Petrini, D. Dascalu, G. Konstantinidis
in "Microwave Circuits and devices based on MEMS technologies"
Series in Micro and Nanoengineering, Publishing House of the Romanian Academy, 2011, pp. 359-365,
Editors: L Tarricone, A Muller, D Dascalu, R Sorrentino, ISBN 978-973-27-2068

[6]. 200 GHz Receiver with Double Folded Slot Antennas Fabricated on Thin GaAs Membrane

D. Neculoiu, A. Stavrinidis, T. Vaha-Heikkila, M. Kantenen, A. Muller, G. Konstantinidis, D. Vasilache, Z.
Chatzopoulos, D. Dascalu
in "Microwave Circuits and devices based on MEMS technologies"
Series in Micro and Nanoengineering, Publishing House of the Romanian Academy, 2011, pp. 315-325,
Editors: L Tarricone, A Muller, D Dascalu, R Sorrentino, ISBN 978-973-27-2068-4

[7]. Acoustic Devices for GHz Applications Based on Micromachining and Nanoprocessing of GaN/Silicon

A. Muller, D. Neculoiu, G. Konstantinidis, D. Vasilache, A. Dinescu, A. Stavrinidis, G. Deligiorgis, M.
Danila, K. Tzagaraki, M. Dragoman, A. Cismaru, C. Buiculescu, I. Petrini, A.A. Muller, D. Dascalu
in "Microwave and millimeter wave MEMS"
Series in Micro and Nanoengineering, Publishing House of the Romanian Academy, 2010, pp. 103-111,
Editors: Flavio Giacomozzi, Alexandru Muller, Dan Dascalu, Robert Plana, ISBN 978- 973-27-1916-9

[8]. 60 GHz Receiver with Double Folded Slot Antennas Fabricated on Thin GaAs Membrane

D. Neculoiu, G. Konstantinidis, T. Vaha-Heikkila, M. Kantenen, A. Muller, A. Stavrinidis, D. Vasilache, Z.
Chatzopoulos, A. Muller, M. Dragoman, D. Dascalu
in "Microwave and millimeter wave MEMS"

Series in Micro and Nanoengineering, Publishing House of the Romanian Academy, 2010, pp. 49-57 Editors:
Flavio Giacomozzi, Alexandru Muller, Dan Dascalu, Robert Plana, ISBN 978- 973-27-1916-9

[9]. Microwave and Millimetre Wave Devices based on Micromachining of III-V Semiconductors

A. Muller, D. Neculoiu, G. Konstantinidis, T. Vaha Heikkila

in "Advanced materials and technologies for micro/nano-devices, sensors and actuators"
Editors E. Gusev, E. Garfunkel, A Dideikin, ISBN 978-90-481-3806-7, ISSN 1874-6500, Springer 2010

[10]. Simple Nanoelectromechanical Systems for Giga – Applications

M. Dragoman, G. Konstantinidis, D. Dragoman, D. Neculoiu, Alina Cismaru, R. Plana, H. Hartnagel, A. Kostopoulos, R. Buiculescu

in "New developments in micro electro mechanical systems for radio frequency and millimeter wave applications"

Series in Micro and Nanoengineering, Publishing House of the Romanian Academy pp 97 – 101, 2009

[1.5]. JOURNAL EDITOR

Guest editor **Microelectronic Engineering**, Volume 112, December 2013

[1.6]. PUBLICATIONS IN CONFERENCE PROCEEDINGS

[1]. Pressure and temperature determination with micromachined GaN/Si SAW based resonators operating in the GHz range

Al. Müller, G. Konstantinidis, A. Stefanescu, I. Giangu, A. Stavriniadis, M. Pasteanu, G. Stavriniadis A. Dinescu

Proceedings of 19th International Conference in Solid-State Sensors, Actuators and Microsystems (TRANSDUCERS 2017)

[2]. Effect of metallization on resonance frequency of III-Nitride SAW structures used in sensor applications

Al. Müller A. Stefanescu, I. Giangu, A. Dinescu, G. Konstantinidis

Proceedings of 2017 International Semiconductor Conference (CAS 2017) pp 127-128

[3]. Cross section spatial doping profiling of 4H-SiC VJFET by various techniques

K. Tsagaraki, M. Nafouti, H. Peyre, K. Vamvoukakis, N. Makris, M. Kayambaki, A. Stavriniadis, G. Konstantinidis, M. Panagopoulou, D. Alquier, K. Zekentes

Proceedings of the International conference on SiC and Related Materials (ICSCRM 2017), Washington DC, USA, 17-22 September 2017

[4]. Pressure sensors based on GHz operating GaN/Si acoustic devices

I. Giangu, G. Stavriniadis, A. Dinescu, N. Kornilios, A. Stavriniadis, A. Stefanescu, M. Pasteanu, G. Konstantinidis, A. Müller

Proceedings of MEMSWAVE 2015, Barcelona, Spain, pp 21-23

[5]. Analysis of temperature dependence of resonance frequencies for surface acoustic wave modes on GaN

A. Müller, I. Giangu, G. Stavriniadis, A. Dinescu, A. Stavriniadis, A. Stefanescu, M. Pasteanu, G. Konstantinidis

Proceedings of MEMSWAVE 2015, Barcelona, Spain, pp 17-20

[6]. Analysis of temperature dependence of resonance frequencies for different SAW type propagation modes on GaN

Al. Muller, I. Giangu, G. Stavriniadis, A. Dinescu, A. Stavriniadis, A. Stefanescu, M. Pasteanu, G. Konstantinidis,

Proceedings of International Semiconductor Conference CAS 2015, 12-14 Oct 2015, Sinaia, Romania

[7]. Pressure sensors based on high frequency operating GaN FBAR

I. Giangu, G. Stavriniadis, A. Stefanescu, A. Stavriniadis, A. Dinescu, G. Konstantinidis, A. Müller

Proceedings of International Semiconductor Conference CAS 2015, 12-14 Oct 2015, Sinaia, Romania, pp 99-102

[8]. GaN/Si Acoustic Devices Towards Sensing Applications

A. Stefanescu, A. Stavriniadis, V. Buiculescu, I. Giangu, F. Bechtold, A. Dinescu, G. Stavriniadis, T. Kostopoulos, G. Konstantinidis, A. Muller

[9]. Monolithic Integration of HEMT with Temperature SAW Based Sensor

T. Kostopoulos, A. Stavrinidis, I. Giangu, G. Stavrinidis, V. Buiculescu, A. Stefanescu, G. Konstantinidis, A. Muller

MEMSWAVE 2014, La Rochelle 1-2 July

[10]. GaN-based SAW structures resonating within the 5.4-8.5 GHz frequency range, for high sensitivity temperature sensors

A. Muller, G. Konstantinidis, I. Giangu, V. Buiculescu, A. Dinescu, A. Stefanescu, A. Stavrinidis, G. Stavrinidis, A. Ziaei

Proceedings International Microwave Symposium IMS 2014, 1-6 June, Tampa, USA, session "THzF: Sensors and Sensor Systems"

[11]. Progress in manufacturing of GaN SAW devices resonating in the GHz frequency

A. Müller, G. Konstantinidis, A. Dinescu, A. Stefanescu, A. Stavrinidis, V. Buiculescu, A. Ziaei

SMART SYSTEMS INTEGRATION 2014, Vienna, 26-27 March 2014, session "Advanced micro and nano technologies"

[12]. Novel humidity and temperature sensors based on GaN/Si acoustic structures for GHz applications

A. Stefanescu, G. Konstantinidis, K. Szaciłowski, V. Buiculescu, I. Giangu, A. Cismaru, A. Dinescu, A. Stavrinidis, G. Stavrinidis, A. Muller

38th Workshop on Compound Semiconductor Devices and Integrated Circuits, 15 – 18 June 2014, Delphi, Greece

[13]. AlN/GaN HEMTs with thin GaN/AlN buffer layers on sapphire (0001) substrates

Ch. Zervos, A. Bairamis, A. Adikimenakis, A. Kostopoulos, M. Kayampaki, K. Tsagaraki, G. Konstantinidis, and A. Georgakilas

WOCSDICE 2014 proceedings, Delfi, Greece, pp. 55-56

[14]. Epitaxial Ga-polarity AlN/GaN (0001) HEMTs on polycrystalline diamond substrates

Al. Georgakilas, K. E. Aretouli, K. Tsagaraki, A. Adikimenakis, A. Kostopoulos, A. Stavrinidis, and G. Konstantinidis

WOCSDICE 2014 proceedings, Delfi, Greece, pp. 91-92

[15]. AlN/GaN/AlN double heterostructures with thin AlN top barriers

Ch. Zervos, A. Bairamis, A. Adikimenakis, A. Kostopoulos, M. Kayambaki, K. Tsagaraki, G. Konstantinidis & A. Georgakilas

ASDAM 2014 Conference Proceedings, pp. 113-116 (IEEE, 2014). IEEE Catalog Number: CFP14469-PRT, ISBN: 978-1-4799-5474-2.

[16]. A study on the fabrication of devices and the characterization of GaN nanowires and the GaN/Si heterojunction

G. Doundoulakis, A. Mparamis, E. Tsikritsaki, A. Stavrinidis, Ch. Zervos, G. Kwnstantinidis, M. Kagiampaki, S. Eftychis, J. E. Kruse, A. Adikimenakis, A. Georgakilas

Workshop on compound semiconductor devices and integrated circuits (WOCSDICE) 2014, Delfi, Greece, pp. 129-130

[17]. Nanopatterning of Si(111) substrates for selective growth of III-nitride nanowires by plasma-assisted molecular beam epitaxy

P. Dimitrakis, A. Olziersky, V. Ioannou Sougleridis, P. Normand, J. E. Kruse, S. Eftychis, G. Doundoulakis, K. Tsagkaraki, M. Androulidaki, G. Konstantinidis, A. Georgakilas

Workshop on compound semiconductor devices and integrated circuits (WOCSDICE) 2014, Delfi, Greece, pp. 131-132

[18]. Single resonator GaN/Si SAW based temperature sensor

A. Muller, G. Konstantinidis, A. Dinescu, A. Stefanescu, A. Cismaru, V Buiculescu, I. Giangu, G. Stavrinidis, A. Stavrinidis
2013 Nanotechnology Conference and Trade Show-Nanotech 2013, vol 2, pp 423 -426, Washington, May 2013

[19]. Novel high sensitivity GaN SAW based temperature sensor structures working in the GHz frequency range

A. Muller, G. Konstantinidis, A. Dinescu, A. Stefanescu, A. Cismaru, I. Giangu, A. Stavrinidis, T. Kostopoulos, V. Buiculescu
EMRS Spring 2013, Symposium L, paper 11.2, Strasbourg, France

[20]. 4H-SiC VJFETs with self-aligned contacts

K. Zekentes, K. Vassilevski, A.B. Horsfall, N.G. Wright, A. Stavrinidis, G. Konstantinidis, M. Kayambaki
Proceedings of "36th Workshop on Compound Semiconductor Device and Integrated Circuits (WOCSDICE 2013)", Germany, 2013, p. 53

[21]. GHz operating GaN/Si SAW based temperature sensor

A. Muller, G. Konstantinidis, A. Dinescu, V Buiculescu, A. Stefanescu, A. Cismaru, I. Giangu, G. Stavrinidis, A. Stavrinidis, A Ziaei,
MEMSWAVE 2013 Potsdam, Germania, 1-3 July 2013, Electronic Proceedings

[22]. High sensitivity GaN SAW based temperature sensor structures working in the GHz frequency range

A. Müller, G. Konstantinidis, A. Dinescu, V Buiculescu, A. Stefanescu, A. Cismaru, I. Giangu, G. Stavrinidis, A. Stavrinidis, A. Ziaei
Therminic'13

[23]. Modeling of SAW Resonators Fabricated on GaN/Si

A. Stefanescu, V. Buiculescu, A. Dinescu, A. Cismaru, A. Muller, G. Konstantinidis, A. Stavrinidis, G. Stavrinidis
IEEE Conference on Microwaves, Communications, Antennas and Electronic Systems – IEEE COMCAS 2013, Tel Aviv, Israel, 21-23 October 2013

[24]. Morphological analysis of GaN membranes obtained by micromachining of GaN/Si

A. Cismaru, A. Muller, F. Comanescu, M. Purica, A. Stefanescu, A. Dinescu, G. Konstantinidis, A. Stavrinidis
2013 IEEE International Reliability Physics Symposium (IRPS) Published: 2013

[25]. MSM photodetector based on gold decorated graphene ink

A. Radoi, A. Cismaru, G. Konstantinidis, M. Dragoman
Graphene, Brussels, 2012, pp.151-152

[26]. Deflection and stress analysis of GaN and AlN thin membranes

A. Cismaru, A. Müller, G. Konstantinidis, M. Purica, F. Comanescu, A. Dinescu, A. Stefanescu, A. Stavrinidis
EMRS 2012

[27]. Gas and humidity sensors based on high frequency acoustic devices manufactured on GaN/Si

A. Cismaru, G. Konstantinidis, K. Szacilowski, A. Müller, A. Stefanescu, A. Stavrinidis, K. Tsagaraki, T. Kostopoulos, D. Neculoiu, G. Stavrinidis, C. Buiculescu, P. Kwolek
Proceedings of the 13th International Symposium on RF MEMS and RF Microsystems, MEMSWAVE 2012, Antalia, July 2012, paper 15 Electronic Proceedings

[28]. New Developments on GaN membrane FBARs

A. Stefanescu, D. Neculoiu, A. Muller, G. Konstantinidis, T. Kostopoulos, A. Stavrinidis, I. Petrini, D. Dascalu
Proceedings of the 13th International Symposium on RF MEMS and RF Microsystems, MEMSWAVE 2012, Antalia, July 2012, paper 17 Electronic Proceedings

- [29]. **Charging and discharging processes in AlN dielectric films deposited by plasma assisted molecular beam epitaxy**
M. Koutsourelis, A. Adikimenakis, L. Michalas, E. Papandreou, A. Pantazis, G. Konstantinidis, A. Georgakilas, G. Papaioannou
2012 International Semiconductor Conference, Vols 1 and 2 Volume: 2 Pages: 281-284 Published: 2012
- [30]. **Dielectric Less and Dimple Less MEMS Capacitive Switches: The Actuation Mechanism**
L. Michalas, M. Koutsourelis, G.J. Papaioannou, G. Stavrinidis, G. Konstantinidis
2012 7th European Microwave Integrated Circuits Conference (EUMIC) Pages: 445-448 Published: 2012
- [31]. **Light harvesting using metallic interdigitated structures modified with Au sputtered graphene**
Radoi, A., Dragoman, M., Cismaru, A., Konstantinidis, G., Dragoman, D.
2012 International Semiconductor Conference, Vols 1 and 2 Volume: 2 Pages: 117-120 Published: 2012
- [32]. **SAW GaN/Si based resonators modelling and experimental validation**
Stefanescu, Muller, A. Konstantinidis, G., Buiculescu, V., Dinescu, A., Stavrinidis, A., Neculoiu, D., Cismaru, A.
2012 International Semiconductor Conference, Vols 1 and 2 Volume: 2 Pages: 193-196 Published: 2012
- [33]. **FBAR and SAW devices on GaN/Si operating in the GHz frequency range**
A. Müller, D. Neculoiu, A. Dinescu, A. Cismaru, A. Stefanescu, C. Buiculescu, I. Petrini, G. Konstantinidis, A. Stavrinidis, G. Deligeorgis, T. Kostopoulos
Proc of Smart System Integration Conf., Dresden 22-23 March 2011, Digital proceedings paper 13
- [34]. **Fabrication of 4H-SiC Static Induction Transistors**
A. Stavrinidis, G. Konstantinidis, M. Kayambaki and K. Zekentes
Proceedings of "20th European Workshop on Heterostructure Technology (HETECH 2011)", Lille, France, November 2011
- [35]. **Metal-Semiconductor-Metal UV Photodetectors Manufactured Using Micromachining and Nano-lithographic Technologies of GaN/Si**
A. Müller, G. Konstantinidis, M. Androulidaki, A. Dinescu, A. Stefanescu, D. Neculoiu, A. Cismaru, A. Stavrinidis
EMRS 2011
- [36]. **Developments in SAW and FBAR devices on GaN/Si operating in the GHz frequency range**
A. Müller, D. Neculoiu, A. Dinescu, I. Petrini, A. Cismaru, A. Stefanescu, C. Buiculescu, G. Konstantinidis, A. Stavrinidis, G. Deligeorgis
Le deuxième colloque francophone PLUridisciplinaire sur les Matériaux, l'Environnement et l'Electronique (PLUMEE 2011), Limoges, France, 30 Mai - 1 Juin 2011
- [37]. **Microphysical characterization of micromachined GaN/Si based structures used in acoustic and photonic device**
A. Cismaru, A. Müller, G. Konstantinidis, M. Purica, F. Comanescu, A. Dinescu, A. Stavrinidis, A. Stefanescu
22nd Proc of Micromechanics and Microsystems Technology Europe MME 2011, paper D64
- [38]. **FEM analysis of GaN based surface acoustic wave resonators**
A. Stefanescu, A. Muller, A. Dinescu, G. Konstantinidis, A. Cismaru, A. Stavrinidis, D. Neculoiu
2011 International Semiconductor Conference, 34th Edition, Vols 1 and 2 Pages: 177-180 Published: 2011
- [39]. **Microwave field effect transistor based on graphene**
M. Dragoman, G. Deligeorgis, D. Neculoiu, D. Dragoman, G. Konstantinidis, A. Cismaru, R. Plana
Proc of International Semiconductor Conference, CAS 2010, Sinaia, Oct 2010, pp279-282
- [40]. **Microwave characterization and DC measurements of CPW line based on a wide graphene sheet**
A. Cismaru, M. Dragoman, D. Neculoiu, D. Dragoman, G. Deligeorgis, G. Konstantinidis
R. Plana

[41]. Morphological characterisation of micromachined film Bulk acoustic resonator structures manufactured on GaN/Si

A. Cismaru, A. Stavrinidis, A. Stefanescu, D. Neculoiu, G. Konstantinidis, A. Müller
Proceedings of the 21-st Micromechanics and Micro-systems Workshop MME 2010, Twente September 2010, pp 281-284

[42]. Membrane supported microwave and millimeter wave circuits based on III-V semiconductor micromachining

A. Muller, G. Konstantinidis, D. Neculoiu
Proceedings HETECH 2010, Fodele, Greece 18-20 Oct 2010

[43]. Micromachining and nanoprocessing of GaN/Silicon for SAW and UV photodetector manufacturing

A. Muller, G. Konstantinidis, D. Neculoiu, A. Dinescu, M. Androulidaki, G. Deligeorgis, A. Stavrinidis, R. Gavrilă, A. Cismaru, M. Carp, A. Stefanescu, A. A. Muller, C. Anton D. Dascalu
Proc of International Semiconductor Conference, CAS 2010, Sinaia, Oct 2010, pp265-268

[44]. Progresses in manufacturing of acoustic devices for GHz applications based on GaN/Si

A. Muller, G. Konstantinidis, D. Neculoiu, A. Dinescu, A. Stavrinidis, G. Deligeorgis, A. Cismaru, D. Vasilache, M. Dragoman, A. A. Muller, A. Stefanescu
Proceedings EMRS 2010, Strasbourg, France

[45]. Recent progresses in acoustic devices on GaN/Si

A. Müller, D. Neculoiu, A. Stavrinidis, T. Kostopoulos, A. Dinescu, A. Cismaru, D. Vasilache, G. Deligeorgis, C. Buiculescu, A.A. Müller, I. Petrini, D. Dascalu, G. Konstantinidis
Proceedings MEMSWAVE 2010, Otranto, Italy

[46]. 200 GHz Receiver with Double Folded Slot Antennas Fabricated on Thin GaAs Membrane

D. Neculoiu, A. Stavrinidis, T. Vaha-Heikkilä, M. Kantenen, A. Muller, G. Konstantinidis, D. Vasilache, Z. Chatzopoulos, D. Dascalu
Proceedings MEMSWAVE 2010, Otranto, Italy

[47]. Application of Physical Characterization Methods during fabrication of 4H-SiC Static Induction Transistors

K. Zekentes, M. Androulidaki, K. Tsagaraki, M. Kayambaki, A. Stavrinidis, G. Konstantinidis
Proceedings of "19th European Workshop on Heterostructure Technology (HETECH 2010)", Fodele, Greece, October 2010, p. 19

[48]. Electromagnetic Propagation in Graphene in the mm-Wave Frequency Range

Neculoiu, D., Deligeorgis, G., Dragoman, M., Dragoman, D., Konstantinidis, G., Cisman, A., Plana, R.
2010 European Microwave Integrated Circuits Conference (EUMIC) Pages: 377-380 Published: 2010

[49]. Acoustic devices and UV photodetectors based on micromachining and nanoprocessing of GaN/silicon

A. Müller, G. Konstantinidis, D. Neculoiu, A. Dinescu, A. Stavrinidis, D. Vasilache, M. Dragoman, M. Kayambaki, M. Androulidaki, G. Deligeorgis, A. Cismaru, K. Tsagaraki, C. Buiculescu, I. Petrini, M. Danila, A. A. Müller
IEEE Sensors, MEMS and Electro-optic Systems (SMEOS) Conference 2009, South Africa

[50]. Microwave and millimetre wave devices based on micromachining of III-V semiconductors

A. Muller, D. Neculoiu, G. Konstantinidis, T. Vaha-Heikkilä
NATO Workshop Advances Materials and Technologies for Micro/nano devices, Sensors and Actuators 29 June- 2 July, St Petersburg, 2009

- [51]. **Acoustic devices for GHz applications based on micromachining and nanoprocessing of GaN/Silicon**
A. Muller, D. Neculoiu, G. Konstantinidis, D. Vasilache, A. Dinescu, A. Stavrinidis, G. Deligiorgis, M. Danila, K. Tzagaraki, M. Dragoman A. Cismaru, C. Buiculescu, I. Petrini, A.A. Muller
EMRS Strasbourg 2009
- [52]. **Negative differential resistances in suspended carbon nanotube structures and graphene**
M. Dragoman, G. Konstantinidis, R. Plana, D. Dragoman, M. Al Ahmad A. Kostopoulos, J.-H. Ting, D. Neculoiu, A. Cismaru, R. Buiculescu
EMRS Strasbourg 2009
- [53]. **60 GHz Receiver with Double Folded Slot Antennas Fabricated on Thin GaAs Membrane**
D. Neculoiu, G. Konstantinidis, T. Vaha-Heikkila, M. Kantenen, A. Muller, A. Stavrinidis, D. Vasilache, Z. Chatzopoulos, A. Muller, M. Dragoman, D. Dascalu
Proc of MEMSWAVE 2009 (10th International Symposium on RF MEMS and RF Microsystems) Trento, pp 33-37, 2009
- [54]. **Micromachined III-N Acoustic Devices for Bacteria Detection**
A.K. Pantazis, E. Gizeli, D. Vasilache, E. Aperathitis, A. Müller, G. Konstantinidis
Proc of MEMSWAVE 2009 (10th International Symposium on RF MEMS and RF Microsystems) Trento, pp63-67
- [55]. **Acoustic devices for GHz applications based on micromachining and nanoprocessing of GaN/Silicon**
A. Muller, D. Neculoiu, G. Konstantinidis, D. Vasilache, A. Dinescu, A. Stavrinidis, G. Deligiorgis, M. Danila, K. Tzagaraki, M. Dragoman, A. Cismaru, C. Buiculescu, I. Petrini, A.A. Muller, D. Dascalu
Proc of MEMSWAVE 2009 (10th International Symposium on RF MEMS and RF Microsystems) Trento, pp59-63
- [56]. **DC and microwave response of a one-atom thick graphene flake**
M. Dragoman, D. Dragoman, G. Deligiorgis, G. Konstantinidis, D. Neculoiu, A. Cismaru, R. Plana
2009 International Semiconductor Conference, Vols 1 and 2, Proceedings Pages: 333-336 Published: 2009
- [57]. **GHz FBAR and SAW resonators manufactured on GaN/Si**
Neculoiu, D., Konstantinidis, G., Vasilache, D., Dinescu, A., Stavrinidis, A., Deligiorgis, G., Danila, M., Tzagaraki, K., Cismaru, A., Buiculescu, C., Petrini, I., Muller, A.A., Dascalu, D.
2009 International Semiconductor Conference, Vols 1 and 2, Proceedings Pages: 319-322 Published: 2009
- [58]. **Investigation of electrical properties of carbon nanotubes**
Stavarache, I., Lepadatu, A., Iancu, V., Dragoman, M., Konstantinidis, G., Buiculescu, R.
2009 International Semiconductor Conference, Vols 1 and 2, Proceedings Pages: 121-124 Published: 2009
- [59]. **Planar Negative Index Materials in the Far Infrared Regime**
T.F. Gundogdu, N. Katsarakis, M. Kafesaki, G. Konstantinidis, C.M. Soukoulis, E. Ozbay
2009 IEEE LEOS Annual Meeting Conference Proceedings, Vols 1and 2 Pages: 561-562 Published: 2009
- [60]. **AlN SAW structures for GHz applications**
Mueller, A., Konstantinidis, G., Neculoiu, D., Dinescu, A., Morosanu, C., Stavrinidis, A., Dragoman, M., Vasilache, D., Buiculescu, C., Petrini, I., Anton, C.
2008 Asia Pacific Microwave Conference (APMC 2008), Vols 1-5 Pages: 1574-1577 Published: 2008
- [61]. **GaAs Membrane-Supported 60 GHz Receiver with Double Folded Slot Antennas**
Neculoiu, D., Konstantinidis, G., Vaha-Heikkila, T., Muller, A., Stavrinidis, A., Kantenen, M., Vasilache, D., Chatzopoulos, Z., Dragoman, M.
2008 Asia Pacific Microwave Conference (APMC 2008), Vols 1-5 Pages: 162-165 Published: 2008
- [62]. **Simple nanoelectromechanical systems for Giga-applications**
M. Dragoman, G. Konstantinidis, D. Dragoman, D. Neculoiu, A. Cismaru, R. Plana, H. Harnagel, A. Kostopoulos, R. Buiculescu
Proc of MEMSWAVE Conference, Greece July 2008

- [63]. **Modelling and Fabrication of FBARs based on Nitrides Micromachined Membranes**
D. Neculoiu, A. Muller, G. Konstantinidis, C. Morosanu, D. Vasilache, A. Kostopoulos, A. Stavrinidis
Proc of MEMSWAVE Conference, Greece July 2008
- [64]. **GaN membrane supported MSM ultraviolet photodetector**
A. Müller, G. Konstantinidis, M. Dragoman, D. Neculoiu, A. Dinescu, M. Androulidaki, M. Kayambaki, A. Stavrinidis, D. Vasilache, C. Buiculescu, I. Petrini, A. Kostopoulos
Proc of MEMSWAVE Conference, Greece July 2008
- [65]. **New Developments on AlN based FBAR and SAW Structures for Applications in the GHz Range**
A. Müller, D. Neculoiu, G. Konstantinidis, A. Dinescu, C. Morosanu, A. Kostopoulos, A. Stavrinidis, M. Dragoman, G. Sajin, A Pantazis, A. Cismaru
Proceedings MRS Spring Meeting 2008, San Francisco, March 2008, pg135
- [66]. **GaN membrane supported UV photo-detectors manufactured using nano-lithographic processes**
A. Müller, G. Konstantinidis, M. Dragoman, D. Neculoiu, A. Dinescu, M. Androulidaki, M. Kayambaki, A. Stavrinidis, D. Vasilache, C. Buiculescu, I. Petrini, A. Kostopoulos
Proc of EMRS 2008, Strasbourg, May 2008
- [67]. **Membrane supported microwave and millimeter wave circuits based on IIIVs micromachining**
A. Müller, G. Konstantinidis, D. Neculoiu
Proceedings of IEEE COMCAS, Tel Aviv, May 2008
- [68]. **Fabrication and characterization of Cr-based Schottky diode on n-type 4H-SiC**
C. Koliakoudakis, J. Dontas, S. Karakalos, M. Kayambaki, S. Ladas, G. Konstantinidis, K. Zekentes, S. Kennou
Proceedings of "17th European Workshop on Heterostructure Technology (HETECH 2008)", Venice, Italy, November 2008, p. 129
- [69]. **Millimeter wave identification: Concept, applications, and demonstrations**
T. Vähä-Heikkilä, P. Pursula, A. Müller, D. Neculoiu, G. Konstantinidis, J. Tuovinen.
Nanosensors and Microsensors for Bio-Systems 2008 Volume: 6931 Published: 2008
- [70]. **RF NEMS based on carbon nanotubes and graphene**
M. Dragoman, G. Konstantinidis, D. Dragoman, D. Neculoiu, A. Cismaru, F. Coccetti, R. Plana, H. Harnagel, A. Kostopoulos, R. Buiculescu
2008 International Semiconductor Conference, Proceedings Pages: 103-106 Published: 2008
- [71]. **SAW and FBAR resonators for GHz applications based on micromachining and nanoprocessing of wide bandgap semiconductors**
A. Muller, G. Konstantinidis, D. Neculoiu, M. Dragoman, A. Dinescu, A. Stavrinidis, D. Vasilache, C. Morosanu
2008 IEEE 25th Convention of Electrical and Electronics Engineers in Israel, Vols 1 and 2 Pages: 561-564 Published: 2008
- [72]. **Ultraviolet MSM photodetector based on GaN micromachining**
Mueller, A., Konstantinidis, G., Dragoman, M., Neculoiu, D., Dinescu, A., Androulidaki, M., Kayambaki, M., Stavrinidis, A., Vasilache, D., Buiculescu, C., Petrini, I., Anton, C., Dascalu, D., Kostopoulos, A.
2008 International Semiconductor Conference, Proceedings Pages: 91-94 Published: 2008
- [73]. **GaAs membrane Supported 60 GHz Receiver with Yagi-Uda antenna**
D. Neculoiu, G. Konstantinidis, D. Neculoiu, G. Konstantinidis, T. Vaha-Heikkila, A. Muller, D. Vasilache, A. Stavrinidis, L. Bary, M. Dragoman, I. Petrini, C. Buiculescu, Z. Hazoupulos, N. Kornilios, P. Pursula, R. Plana, D. Dascalu
Proc of the MEMSWAVE Conference, Barcelona, Spain, June, 26-29, 2007. pp15-18

[74]. Micromachined AlN based FBAR structures

D. Vasilache, G. Konstantinidis, D. Neculoiu, C. Morosanu, A. Stavrinidis, A. Kostopoulos, A. Cismaru, C. Buiculescu, A. Muller

Proc of Micromechanics Europe MME 2007, 16-18 Sept, Guimaraes, Portugal, pp39-42, ISBN 978-972-98603-3-1

[75]. 60 GHz band RF MEMS switch

Vasilache, D., Dragoman, M., Constantinidis, G., Psychias, Y., Vladoianu, F., Kostopoulos, T., Tibeica, C., Bary, L., Cismaru, A., Neculoiu, D., Buiculescu, C., Petrini, I., Plana, R., Muller, A.

2006 International Semiconductor Conference, Vols 1 and 2 Pages: 119-122 Published: 2007

[76]. A miniaturized delay line based on slow-wave substrates

Prodromakis, T., Papavassiliou, Ch., Konstantinidis, G.

2007 IEEE International Symposium on Circuits and Systems, Vols 1-11 Pages: 369-372 Published: 2007

[77]. Carbon nanotubes-based microwave and millimeter wave sensors

M. Dragoman, A. Muller, D. Neculoiu, G. Konstantinidis, K. Grenier, D. Dubuc, L. Bary, R. Plana, H. Hartnagel, E. Fourn, E. Flahaut

2007 European Microwave Conference, Vols 1-4 Pages: 16-19 Published: 2007

[78]. GaN membrane MSM ultraviolet photodetectors

A. Muller, G. Konstantinidis, A. Kostopoulos, M. Dragoman, D. Neculoiu, M. Androulidaki, M. Kayambaki, D. Vasilache, C. Buiculescu, I. Petrini

Micro- and Nanotechnology: Materials, Processes, Packaging, and Systems III Volume: 6415 Pages: 41509 Published: 2007

[79]. Membrane supported ALN FBAR structures obtained by micromachining of high resistivity silicon

D. Neculoiu, D. Vasilache, G. Konstantinidis, C. Morosanu, A. Stavrinidis, A. Kostopoulos, A. Cismaru, C. Buiculescu, I. Petrini, A. Muller.

International Semiconductor Conference, Vols 1 and 2, Proceedings Pages: 293-296 Published: 2007

[80]. Micro-scale lowpass filters based on the Maxwell-Wagner phenomenon

Prodromakis, T., Papavassiliou, Ch., Konstantinidis, G.

2007 European Microwave Conference, Vols 1-4 Pages: 850-853 Published: 2007

[81]. Microwave FBAR structures fabricated using micromachined GaN membranes

Neculoiu, D., Konstantinidis, G., Muller, A., Kostopoulos, A., Vasilache, D., Mutamba, K., Sydlo, C., Hartnagel, Hans L., Bary, L., Plana, R

2007 IEEE/MTT-S International Microwave Symposium Digest, Vols 1-6 Pages: 876-879 Published: 2007

[82]. Millimeter wave monolithic integrated receivers based on GaAs micromachining

G. Konstantinidis, D. Neculoiu, A. Stavrinidis, Z. Chatzopoulos, A. Muller, K. Tsagaraki, D. Vasilache, I. Petrini, C. Buiculescu, L. Bary, R. Plana

Micro- and Nanotechnology: Materials, Processes, Packaging, and Systems III Volume: 6415 Pages: C4150 Published: 2007

[83]. Negative bi-exciton binding energy in (211) B InAs/GaAs piezoelectric quantum dots

Dialynas, G. E., Xenogianni, C., Trichas, E. Savvidis, P.G., Constantinidis, G., Hatzopoulos, Z., Pelekanos, N.T.

2007 Conference on Lasers & Electro-Optics/quantum Electronics and Laser Science Conference (Cleo/qels 2007), Vols 1-5 Pages: 1793-1794 Published: 2007

[84]. Wide band gap semiconductor SAW type devices for GHz applications, manufactured using nano-lithographic techniques

Muller, A., Dinescu, A., Konstantinidis, G., Vasilache, D., Dragoman, M., Morosanu, C., Sajin, G., Neculoiu, D.

2007 International Semiconductor Conference, Vols 1 and 2, Proceedings Pages: 255-258 Published: 2007

[85]. Membrane supported millimeter wave circuits based on silicon and GaAs micromachining

A. Müller, D. Neculoiu, G. Konstantinidis, R. Plana

Proc of Mediterranean Microwave Symposium, Genova, September 2006

[86]. Membrane supported Yagi-Uda mm-wave antennas

D. Neculoiu, A. Muller, D. Vasilache, G. Konstantinidis, A. Staviniidris, P. Pons, L. Bary, R. Plana

European Conference on Antennas and Propagation-Book of abstracts, Nice, France, 9-10 Nov, 2006, pp78-79

[87]. GaAs Micromachining Technologies for High Performance Millimeter Wave Communication Systems

A. Müller, D. Neculoiu, G. Konstantinidis, A. Stavriniidris, D. Vasilache, A. Kostopoulos, Z. Hazoupulos, C. Buiculescu, I. Petrini, L. Bary, R. Plana, D. Dascalu

Matehn '06- 4th International Conference on materials and manufacturing technologies, Cluj-Napoca, Romania, Sept 2006

[88]. Membrane supported millimeter wave circuits based on silicon and GaAs micromachining

A. Müller, D. Neculoiu, G. Konstantinidis, R. Plana

CMOS Emerging Technologies Workshop, Research & Business Opportunities Ahead, July 19-21, 2006, Banff, Alberta, Canada

[89]. GaAs membrane-supported Yagi-Uda antenna 45 GHz receiver

A. Staviniidris, A. Muller, D. Neculoiu, G. Konstantinidis, D. Vasilache, M. Dragoman, I. Petrini, C. Buiculescu, Z. Chatzopoulos, L. Bary, R. Plana

Proc of the MEMSWAVE Conference, Orvieto, Italy, 2006, pp 16-20

[90]. New developments of GaN membrane based FBAR structures

D. Neculoiu, A. Muller, D. Vasilache, D. Dascalu, G. Konstantinidis, A. Kostopoulos, A. Adikimenakis, A. Georgakilas, K. Mutamba, C. Sydlo, H. L. Hartnagel

Proc of the MEMSWAVE Conference, Orvieto, Italy, 2006, pp. 51-54

[91]. Micromachined GaN-based FBAR Structures for Microwave Applications

Kabula Mutamba, Dan Neculoiu, Alexandru Muller, George Konstantinidis, Dan Vasilache, Cesary Sydlo, A. Kostopoulos, A. Adikimenakis, A. Georgakilas and Hans Ludwig Hartnagel

Proc of Asia Pacific Microwave Conference, Yokohama, Dec 2006, pp. 3-1757-1760

[92]. Design and Characterization of a 45 GHz Yagi-Uda Antenna Receiver Fabricated on GaAs Micromachined Membrane

D. Neculoiu, G. Konstantinidis, A. Muller, A. Staviniidris, D. Vasilache, Z. Chatzopoulos, L. Bary, R. Plana

Proc of Asia Pacific Microwave Conference, Yokohama, pp 3-1653-1656, Dec 2006

[93]. Millimeter -wave monolithic integrated receivers based on GaAs micromachining

G. Konstantinidis, D. Neculoiu, A. Staviniidris, Z. Chatzopoulos, A. Muller, K. Tsagaraki, D. Vasilache, I. Petrini, C. Buiculescu, L. Bary, R. Plana

Proc of the SPIE Conf on Smart Materials Nano and Microsystemws 10 -13 December Adelaide 2006

[94]. GaN membrane MSM ultraviolet photodetectords

A. Muller, G. Konstantinidis, D Neculoiu, A. Kostopoulos, M. Dragoman, M. Androulidaki, M. Kayambaki, D. Vasilache, C. Buiculescu, I. Petrini

Proc of the SPIE Confon Smart Materials Nano and Microsystemws 10 -13 December Adelaide 2006

[95]. Millimeter wave MEMS switch for 60 GHz band

D. Vasilache, M. Dragoman, G. Konstantinidis, Y. Psychias, F. Vladioianu, A. Kostopoulos, C. Tibeica, L. Barry, A. Cismaru, D. Neculoiu, C. Buiculescu, I. Petrini, R. Plana, A. Müller

Proc of Micromechanics Europe MME 2006, Southampton, Sept 2006, pp213-216

[96]. Electromagnetic modelling of GaAs membrane supported mm-wave receivers

Neculoiu, D., Muller, A., Konstantinidis, G.

International MEMS Conference 2006 Volume: 34 Pages: 28-33 Published: 2006

[97]. Heterogeneous integration technique of optoelectronic dies to CMOS circuits via metallic bonding

Robogiannakis, P., Kyriakis-Bitaros, E.D., Minoglou, K., Katsafouros, S., Kostopoulos, A., Konstantinidis, G., Halkias, G.

ESTC 2006: 1st Electronics System Integration Technology Conference, Vols 1 and 2, Proceedings Pages: 328-333 Published: 2006

[98]. Microwave p-i-n diodes and switches based on 4H-SiC

Camara, N., Zekentes, K., Romanov, L.P. Kirillov, A.V., Boltovets, M.S., Vassilevski, K.V., Haddad, G. 2006 *European Microwave Conference, Vols 1-4 Pages: 1525-1528 Published: 2006*

[99]. Technology, Properties and Limitations of State-of-the-art InAlN/GaN HEMTs

J. Kuzmík, J. -F. Carlin, T. Kostopoulos, G. Konstantinidis, A. Georgakilas, D. Pogany

63rd Device Research Conference (DRC '05), Conference digest pp. 57-58, Santa Barbara, June 20-22, 2005

[100]. Surface and bulk micromachining techniques for lumped components filters manufacturing

F. Giacomozzi, B. Margesin, I. Petrini, D. Vasilache, D. Neculoiu, C. Buiculescu, A. Müller, G. Konstantinidis, T. Vähä-Heikkilä, T Kostopoulos, Y. Psychias

Proceedings MEMSWAVE Workshop, Lausanne 2005

[101]. Electromagnetic modeling of GaN FBAR structures

D. Neculoiu, G. Konstantinidis, K. Mutamba, A. Takacs, D. Vasilache, C. Sydlo, T. Kostopoulos, A. Stavriniadis, A. Muller

Proceedings MEMSWAVE Workshop, Lausanne 2005

[102]. Millimeter-wave passive circuit elements based on GaAs micromachining

A. Pantazis, D. Neculoiu, Z. Hazopulos, D. Vasilache, M. Lagadas, M. Dragoman, C. Buiculescu, I. Petrini, A. A. Muller, G. Konstantinidis A. Muller

Micromechanics and Microengineering, vol.15, no.8, 2005

[103]. Electromagnetic modeling of micromachined GaN thin films for FBAR applications

D. Neculoiu, G. Konstantinidis, K. Mutamba, A. Takacs, D. Vasilache, C. Sydlo, T. Kostopoulos, A. Stavriniadis, A. Muller

International Semiconductor Conference Vol 1 and 2 Pages: 119-122 Published: 2005

[104]. Investigation of thermally activated charging effects in RF-MEMS switches

Exarchos, M., Theonas, V., Papaioannou, G. J., Constantinidis, G., Psychias, S., Vasilache, D., Dragoman, M., Muller, A., Neculoiu, D.

International Semiconductor Conference Vol 1 and 2 Pages: 175-178 Published: 2005

[105]. RF MEMS sensitivity to electromagnetic radiation

Theonas, V. G., Exarchos, M., Konstantinidis, G., Papaioannou G. J.

Second Conference on Microelectronics, Microsystems and Nanotechnology Volume: 10 Pages: 313-316 Published: 2005

[106]. Yagi-Uda antennas fabricated on thin GaAs membrane for millimeter wave applications

Neculoiu, D., Konstantinidis, G., Bary, L., Vasilache, D., Stavriniadis, A., Hazopulos, Z., Pantazis, A., Plana, R., Muller, A.

2005 IEEE International Workshop on Antenna Technology: Small Antennas Novel MetaMaterials, Proceedings Pages: 418-421 Published: 2005

[107]. New Millimeter Wave Circuits Based on GaAs Micromachining

A. Pantazis, D. Neculoiu, Z. Hazopulos, D. Vasilache, M. Lagadas, M. Dragoman, C. Buiculescu, I. Petrini, A. Müller, G. Konstantinidis, A. Müller

Proc of 15th MicroMechanics Europe Workshop, 5-7Sept 2004, Leuven, pp 245-248

[108]. Design and technology for III-V (arsenides, nitrides) membrane supported Yagi-Uda antenna

G. Konstantinidis, A. Muller, Z. Chatzopoulos, D. Neculoiu, A. Kostopoulos, A. Georgakilas, A. Adikimenakis, D. Vaschilache, M. Lagadas

[109]. ZrO₂/GaN metal oxide semiconductor structures characterization and application

J. Kuzmik, S. Harasek, G. Konstantinidis, Š. Haščík, D. Pogany, E. Bertagnolli, and A. Georgakilas
28th Workshop on Compound Semicond. Devices and Integrated Circuits held in Europe (WOCS-DICE'04), May 17-19, 2004, Smolenice, Slovakia, pp. 35-36

[110]. A micromachined 38 GHz Schottky-diode uniplanar monolithic integrated quasi-optical mixer

Neculoiu, D., Bartolucci, G., Konstantinidis, G., Marcelli, R., Petrini, I., Dragoman m., Vasilache, D., Muller, A.
2004 IEEE Radio Frequency Integrated Circuits (RFIC) Symposium, Digest of Papers Pages: 531-534 Published: 2004

[111]. Novel micromachined GaAs circuits for millimeter wave applications

Muller A., Konstantinidis G., Neculoiu D., Vasilache D., Hatzopoulos Z., Pantazis A., Stavriniadis A., Buiculescu C., Petrini I.
EDMO 2004: 12th IEEE International Symposium on Electron Devices for Microwave and Optoelectronic Applications Pages: 9-14 Published: 2004

[112]. RF MEMS sensitivity to radiations

Papaioannou, G. J., Theonas, V., Exarchos, M., Konstantinidis, G.
34th European Microwave Conference, Vols 1-3, Conference Proceedings Pages: 65-68 Published: 2004

[113]. GaAs membrane supported millimeter wave circuits

A. Muller, G. Konstantinidis, D. Neculoiu, M. Lagadas, G. Deligeorgis, D. Vasilache, L. Bary, R. Plana, I. Petrini, C. Buiculescu, N. Kornilios
International Semiconductor Conference, Vols 1 and 2, Proceedings Pages: 57-60 Published: 2003

[114]. GaAs MEMS for millimeter wave communications

Muller, A., Konstantinidis, G., Neculoiu, D., Plana, R.
33rd European Microwave Conference, Vols 1-3, Conference Proceedings Pages: 33-36 Published: 2003

[115]. On the alpha particle induced degradation in n-type GaAs layers

N. Arpatzanis, G. Constantinidis, A. Georgakilas, G. J. Papaioannou, M. Papastamatiou
12th International Conference on Semiconducting & Insulating Materials (SIMC-XII-2002), pp. 159-164 (IEEE, 2002)

[116]. On the alpha particle induced degradation in n-type GaAs layers

N. Arpatzanis, G. Constantinidis, A. Georgakilas, G. J. Papaioannou, M. Papastamatiou
12th International Conference on Semiconducting & Insulating Materials Pages: 159-164 Published: 2002

[117]. GaAs membrane supported millimeter wave filters

G. Konstantinidis, A. Mueller, G. Deligiorgis, I. Petrini, D. Vasilache, D. Neculoiu, M. Lagadas, C. Buiculescu, V. Avramescu, S. A. Iordanescu, P. Blondy, H. Helvajian, S. W. Janson, F. Laermer.
MEMS Components and Applications for Industry, Automobiles, Aerospace, and Communication Volume: 4559 Pages: 157-163 Published: 2001

[118]. Investigation of different Si (111) substrate preparation methods for the growth of GaN by radio frequency plasma-assisted molecular beam epitaxy

M. Androulidaki, K. Amimer, K. Tsagaraki, G. Constantinidis, Z. Hatzopoulos, A. Georgakilas, F. Peiro and A. Cornet
Microelectronics, Microsystems and Nanotechnology (MMN 2000), pp. 197-200 (Word Scientific, 2001)

[119]. Material properties of GaN films with Ga- or N-face polarity grown by MBE on Al₂O₃ (0001) substrates under different growth conditions

At. Kostopoulos, S. Mikroulis, E. Dimakis, E.-M. Pavelescu, K. Tsagaraki, G. Constantinidis, A. Georgakilas, Ph. Komninou, Th. Kehagias and Th. Karakostas
Microelectronics, Microsystems and Nanotechnology (MMN 2000), pp. 201-204 (Word Scientific, 2001)

[120]. GaAs micromachining for millimeter wave applications

A. Muller, G. Constantinidis, D. Neculoiu, D. Vasilache, M. Lagadas, G. Deligeorgis, S. Iordanescu
International Semiconductor Conference, Vols 1 and 2, Proceedings Pages: 25-28 Published: 2001

[121]. Atomic force microscopy analysis of Ga-face and N-face GaN grown on Al₂O₃ (0001) by plasma-assisted molecular beam epitaxy

At. Kostopoulos, S. Mikroulis, E. Dimakis, K. Tsagaraki, G. Constantinidis and A. Georgakilas
Proceedings of ASDAM 2000, "The Third Int. EuroConference on Advanced Semiconductor Devices and Microsystems, Smolenice, Slovakia, 16-18 October, 2000", pp. 355-358 (IEEE, Piscataway, NJ, 2000 – IEEE Catalog. No. 00EX386)

[122]. Material properties of GaN grown by radio frequency plasma-assisted molecular beam epitaxy on Si (111) substrates

M. Androulidaki, K. Amimer, K. Tsagaraki, M. Kayambaki, G. Constantinidis, Z. Hatzopoulos and A. Georgakilas
Proceedings of ASDAM 2000, "The Third Int. EuroConference on Advanced Semiconductor Devices and Microsystems, Smolenice, Slovakia, 16-18 October, 2000", pp. 9-12 (IEEE, Piscataway, NJ, 2000 – IEEE Catalog. No. 00EX386)

[123]. Atomic force microscopy analysis of Ga-face and N-face GaN grown on Al₂O₃ (0001) by plasma-assisted molecular beam epitaxy

Kostopoulos, A, Mikroulis, S., Dimakis, E., Tsagaraki, K., Constantinidis, G., Georgakilas, A.
ASDAM 2000: Third International Euroconference on Advanced Semiconductor Devices and Microsystems - Conference Proceedings Pages: 355-358 Published: 2000

[124]. Improvement of uniformity in conventional RIE process for via hole fabrication in GaAs based MMIC's

Deligeorgis, G, Lagadas, M, Constantinidis, G,
2000 International Semiconductor Conference, Vols 1 and 2, Cas 2000 Proceedings Pages: 163-166 Published: 2000

[125]. Material properties of GaN grown by radio frequency plasma-assisted molecular beam epitaxy on Si (111) substrates

Androulidaki, M., Amimer, K., Tsagaraki, K., Kayambaki, M., Mikroulis, S., Constantinidis, G., Hatzopoulos, Z., Georgakilas, A.
ASDAM 2000: Third International Euroconference on Advanced Semiconductor Devices and Microsystems - Conference Proceedings Pages: 9-12 Published: 2000

[126]. Microphysical characterization and residual stress analysis of thin polyimide membranes on GaAs substrate, support for micromachined structures

I. Petrini, A. Muller, S. Iordanescu, D. Vasilache, G. Constantinidis, F. Giacomozzi, C. Anton
2000 International Semiconductor Conference, Vols 1 and 2, Cas 2000 Proceedings Pages: 455-458 Published: 2000

[127]. Thin membrane supported millimeter wave micromachined filters

Muller, A, Constantinidis, G., Giacomozzi, F., Lagadas, M., Deligeorgis, G., Iordanescu, S., Petrini, I., Vasilache, D., Marcelli, R., Bartolucci, G., Neculoiu, D., Blondy, P., Dascalu, D.
2000 International Semiconductor Conference, Vols 1 and 2, Cas 2000 Proceedings Pages: 429-432 Published: 2000

[128]. Direct MBE growth of GaN on GaAs substrates for integrated short wavelength emitters

Al. Georgakilas, K. Tsagaraki, E. Makarona, G. Constantinidis, M. Androulidaki, M. Kayambaki, E. Aperathitis and N.T. Pelekanos
E-MRS 1999 Spring Meeting, June 1-4, 1999, Strasbourg, France, CD-ROM Proceedings, Symposium K, paper K/P02

[129]. Effects of Silicon Misorientation Angle on the RF and DC Characteristics of GaAs-on-Si MESFETs

Ch. Papavassiliou, G. Constantinidis, N. Kornilios, A. Georgakilas, E. Lochtermann and P. Panayotatos

"Strained Layer Epitaxy-Materials, Processing and Device Applications", *Mater. Res. Soc. Symp. Proc.*, Vol. 379, pp. 345-350 (MRS, Pittsburgh, 1995) eds. J. Bean, E.A. Fitzgerald, J. Hoyt and K.Y. Cheng

[130]. Molecular Beam Epitaxy of InGaAs on Si

Al. Georgakilas, A. Dimoulas, G. Constantinidis, K. Tsagaraki, J. Stoemenos, A.A. Iliadis, and A. Christou

Crystal Properties and Preparation, Vol. 36-38, pp. 407-416 (1991); also in the *Proceedings of the "3rd European Conference on Crystal Growth (ECCG-3), Budapest, Hungary, 5-11 May, 1991"*, Vol. 2 (ISBN 0-87849-545-2 - Trans Tech Publications Inc., Switzerland, 1991), ed. A. Lorinczy

[131]. Compositional and electronic changes in Bridgman ingots of CuInSe₂

Tomlinson R.D., Al-Saffar I.S., Constantinidis G., Hill A.E., Imaneh M., Pilkington R.D., Smith J.J
Proc. 8th European Photovoltaic Energy Conference, Florence 1988 Published: 1988

[2]. CONFERENCE PRESENTATIONS

[2.1]. INVITED CONFERENCE PRESENTATIONS

[1]. Wide band gap technology

Konstantinidis G

International Semiconductor Conference, Sinaia, Romania, October 2005

[2]. III-V micromachining for RF MEMS

Konstantinidis G

WOCKSDICE 2004, Smolenice castle, Slovakia, May 2004

[3]. GaAs MEMS for millimeter wave communications

Konstantinidis G and A. Muller

European Microwave Week, Munich, Germany, October 2003

[4]. SiC technologies

Konstantinidis G.

International Semiconductor Conference, Sinaia, Romania, October 1997

[2.2]. CONTRIBUTION TO INVITED CONFERENCE PRESENTATIONS

[5]. Graphene ballistic high frequency integrated circuits

G. Deligeorgis, R. Yakimova, G. Stavrinidis and G. Konstantinidis

12th International Conference on Nanosciences & Nanotechnologies – NN15, 7 – 1 July 2015 Thessaloniki, Greece

[6]. Analysis of temperature dependence of resonance frequencies for different SAW type propagation modes on GaN

A. Müller, I. Giangu, G. Stavrinidis, A. Dinescu, A. Stavrinidis, A. Stefanescu, M. Pasteanu, G. Konstantinidis

International Semiconductor Conference CAS 2015, 12-14 Oct 2015, Sinaia, Romania

[7]. Carbon based RF circuits fabrication, putting Silicon aside

G. Deligeorgis and G. Konstantinidis

44th European Microwave conference, Workshop on Advances in the 'Carbon Smart Systems for Wireless Applications' WM8, 5-10 October 2014 Rome, Italy

[8]. Novel sensing devices based on micromachining and nanoprocessing of compound semiconductors

A. Muller, G. Konstantinidis

MEMSWAVE 2014, La Rochelle 1-2 July

[9]. Graphene electronics past present and future

G. Deligeorgis, F. Coccetti, G. Konstantinidis and R. Plana

Conference on Nanoscience and Nanotechnology 2012, 1 – 4 October 2012 Frascati, Italy

- [10]. **Acoustic and photonic devices based on micromachining and nanoprocessing of GaN/Si**
A. Müller, G. Konstantinidis
5th International Conference on Micro-Nanoelectronics, Nanotechnology and MEMS, Oct 2012, Heraklion, Greece
- [11]. **Harvesting graphene's properties for nanoelectronics**
G. Deligeorgis, F. Coccetti, G. Konstantinidis and R. Plana
9th International Conference on Nanosciences & Nanotechnologies – NN12, 3 – 6 July 2012 Thessaloniki, Greece
- [12]. **Graphene Devices for microwave and terahertz applications**
M. Dragoman, G. Konstantinidis, G. Deligeorgis, D. Neculoiu, D. Dragoman, A. Cismaru, R. Plana
WOCSDICE, Catania, Italia, 2011
- [13]. **Progresses in manufacturing of acoustic devices for GHz applications based on GaN/Si using micromachining and nano-lithographic technologies**
A. Muller, D. Neculoiu, A. Dinescu, D. Dascalu, G. Konstantinidis, T. Kostopoulos, A. Stavrinidis
12th International Symposium on RF MEMS and RF Microsystems Athens, June 2011
- [14]. **Progress in Graphene Based Devices and Sensors**
G. Deligeorgis, F. Coccetti, G. Konstantinidis, M. Dragoman, R. Plana
2011 IEEE MTT-S International Microwave Symposium (IMS 2011) Workshop on Nanotechnology-enabled RF and Cognitive Devices, Components and Systems (WFJ), 5 – 10 June 2011 Baltimore, USA
- [15]. **Graphene transistors, present and challenges**
M. Dragoman, G. Deligeorgis, D. Neculoiu, D. Dragoman, G. Konstantinidis, A. Cismaru, R. Plana
European Microwave conference, Workshop on Nanotechnologies WFS02, 25-29 September 2010 Paris, France
- [16]. **Fabrication of graphene devices, issues and prospects**
G. Deligeorgis, G. Konstantinidis, M. Dragoman, R. Plana
33rd International Semiconductor Conference CAS, 10-14 October 2010 Sinaia, Romania
- [17]. **InAlN-based HEMT for Microwave Applications**
Sylvain L. Delage, N. Sarazin, M.-A. diForte-Poisson, J.-C. Jaquet, C. Dua, E. Morvan, C. Giesen, M. Heuken, B. Schineller, J.-F. Carlin, M. Gonschorek, N. Grandjean, M. Py, A. Georgakilas, E. Iliopoulos, G. Konstantinidis, K. Cico, K. Fröhlich, J.-C. De Jaeger, C. Gaquière, E. Kohn, M. Alomari, F. Medjoub, J. Kuzmik, D. Pogany, G. Pozzovivo
8th Topical Workshop on Heterostructure Microelectronics”, August 25-28, 2009, Nagano, Japan
- [18]. **InAlN/GaN heterostructures for microwave power and beyond**
E. Kohn, M. Alomari, A. Denisenko, M. Dipalo, D. Maier, F. Medjdoub, C. Pietzka, S. L. Delage, M.-A. diForte-Poisson, E. Morvan, N. Sarazin, J.-C. Jaquet, C. Dua, J.-F. Carlin, N. Grandjean, M. A. Py, M. Gonschorek, J. Kuzmik, D. Pogany, G. Possovivo, C. Ostermaier, L. Toth, B. Pecz, J.-C. De Jaeger, C. Gaquière, K. Cico, K. Fröhlich, A. Georgakilas, E. Iliopoulos, G. Konstantinidis, C. Giesen, M. Heuken and B. Schineller
2009 Int. Electron Devices Meeting” (IEDM 2009), December 7-9, 2009, Baltimore, USA
- [19]. **Near room temperature GaAs polariton LED,**
S.I. Tsintzos, P.G. Savvidis, G. Konstantinidis, Z. Hatzopoulos, N.T. Pelekanos
29th International Conference on the Physics of Semiconductors (ICPS 09, Rio De Janeiro, Brazil, July 2008)
- [20]. **InAlN/(In)GaN HEMTs for high power applications**
J. Kuzmik, J.-F. Carlin, T. Kostopoulos, G. Konstantinidis, S. Bychikhin, A. Georgakilas, D. Pogany
MIKON 2006, Workshop on GaN Devices, May 25, 2006, Krakow, Poland
- [21]. **III-nitride nanostructures: epitaxy and technology issues**
Al. Georgakilas, N. Pelekanos, G. Konstantinidis, E. Aperathitis, Ph. Komninou and N. Chaniotakis
Joint Greek-PHANTOMS Symposium on Nanotechnology”, NCSR Demokritos, Athens, Greece, February 4, 2004

[22]. Recent developments in membrane supported millimeter wave circuits

A. Muller, D. Neculoiu, G. Konstantinidis, R. Plana

CAS International Conf, Sinaia, Oct 2004

[2.3]. CONTRIBUTED CONFERENCE PRESENTATIONS (FROM 2005)

[23]. Magnetolectric GaN film bulk acoustic wave resonator

A. Bunea, D. Neculoiu, G. Konstantinidis, T. Kostopoulos, A. Stavriniadis, G. Stavriniadis
2019 Asia-Pacific Microwave Conference (APMC), Singapore 10 - 13 December 2019

[24]. Polariton lasing in non-polar GaN/AlGaIn quantum well microcavities

E. A. Amargianitakis, G. Stavriniadis, A. Kostopoulos, G. Konstantinidis, E. Delamadeleine, E. Monroy and N. T. Pelekanos
PLMCN20, International Conference on Physics of Light-Matter Coupling in Nanostructures, Moscow & Suzdal - Russia | July 2-6, 2019

[25]. 4H-SiC Nanowire arrays formation by nanoimprint lithography, plasma etching and sacrificial oxidation

M. Cottat, A. Stavriniadis, C. Gourgon, M. Androulidaki, E. Bano, G. Konstantinidis, J. Boussey, K. Zekentes
Wocksdice 2019, 7-19 Jun 2019 Cabourg (France)

[26]. Transferrable dielectric DBR membranes for versatile GaN-based polariton and VCSEL technology

E.A. Amargianitakis, S. Kazazis, G. Doundoulakis, G. Stavriniadis, G. Konstantinidis, E. Delamadeleine, E. Monroy and N.T. Pelekanos
45th International Conference on Micro & Nano engineering, September 2019, Rhodes, Greece

[27]. Study of the fabrication of vertical GaN nanowire transistors

G. Doundoulakis, A. Adikimenakis, A. Stavriniadis, K. Tsagaraki, M. Androulidaki, F. Iacovella, G. Deligeorgis, G. Konstantinidis and A. Georgakilas
45th International Conference on Micro & Nano engineering, September 2019, Rhodes, Greece

[28]. Substrate effects in selective area growth of GaN nanowires by plasma-assisted molecular beam epitaxy

G. Doundoulakis, A. Adikimenakis, A. Stavriniadis, K. Tsagaraki, M. Androulidaki, G. Deligeorgis, G. Konstantinidis and A. Georgakilas
45th International Conference on Micro & Nano engineering, September 2019, Rhodes, Greece

[29]. Sputtered ZnO nanostructure homojunctions fabricated on room temperature pre-patterned substrates

G. Deligeorgis, V. Kampylafka, A. Kostopoulos, K. Tsagaraki, V. Kontomitrou, G. Konstantinidis, E. Aperathitis, M. Gagaoudakis, G. Kiriakidis
45th International Conference on Micro & Nano engineering, September 2019, Rhodes, Greece

[30]. Cell compatibility study of SU-8 microneedles based wearable dry electrodes for electroencephalogram

G. Kaklamani, G. Stavriniadis, K. Michelakis, V. Kontomitrou, K. Tsagaraki, N. Kornilios and G. Konstantinidis
45th International Conference on Micro & Nano engineering, September 2019, Rhodes, Greece

[31]. Thermally Activated Discharging Mechanisms in SiN_x Films with Embedded CNTs for RF MEMS Capacitive Switches

M. Koutsourelis, G. Stavriniadis, D. Birmpiliotis, G. Konstantinidis and G. Papaioannou
45th International Conference on Micro & Nano engineering, September 2019, Rhodes, Greece

[32]. Charging properties of SiN_x embedded CNTs for MEMS capacitive switches application

D. Birbiliotis, E. Koutsourelis, G. Stavriniadis, G. Konstantinidis, G. Papaioannou
7th International Conference "Micro&Nano 2018" 5- 7 November 2018, Thessaloniki, Greece

- [33]. **The influence of metallization on resonance frequency and temperature sensitivity of GHz operating III-Nitride SAW based sensor structures**
Al. Muller, A. Stefanescu, A. Dinescu, G. Konstantinidis
2018 IEEE/MTT-S International Microwave Symposium - IMS 2018, 10-15 June 2018, Philadelphia, USA
- [34]. **Temperature accelerated discharging process in SiN_x films with embedded CNTs for applications in MEMS switches**
D. Birmpiliotis, G. Stavriniadis, G. Konstantinidis and G. Papaioannou
20th edition of the Symposium on Design, Test, Integration & Packaging of MEMS and MOEMS, DTIP 2018, 22-25 May 2018, Rome, Italy
- [35]. **Nanoscale analysis of Al thin films on (001) GaAs**
Is. Vasiliadis, Th. Kehagias, G.P. Dimitrakopoulos, Z. Chatzopoulos, Ph. Komninou G. Konstantinidis
International conference on extended defects in semiconductors (EDS 2018), 24-29 June 2018, Thessaloniki, Greece
- [36]. **Technology roadmap towards flexible power RF transceivers**
G. Stavriniadis, V. Kontomitrou¹, A. Ziaei, Th. Kehagias, G.P. Dimitrakopoulos, Ph. Komninou G. Konstantinidis
International conference on extended defects in semiconductors (EDS 2018), 24-29 June 2018, Thessaloniki, Greece
- [37]. **Evaluation and understanding of size effects on the conductivity of spontaneously grown GaN nanowires**
G. Doundoulakis, A. Stavriniadis, S. Eftychis, M. Androulidaki, K. Tsagaraki, M. Kayambaki, G. Konstantinidis and A. Georgakilas,
EUROMAT 2017, 17-22 September 2017, Thessaloniki, Greece.
- [38]. **InN field effect transistor with in situ SiN gate dielectric**
Ch. Zervos, A. Adikimenakis, P. Beleniotis, A. Kostopoulos, M. Kayambaki, K. Tsagaraki, G. Konstantinidis, A. Georgakilas,
EUROMAT 2017, 17-22 September 2017, Thessaloniki, Greece.
- [39]. **Patterned substrates for the fabrication of sputtered ZnO-based transparent bipolar devices,**
A. Kostopoulos, G. Konstantinidis, M. Modreanu, M. Kayambaki, K. Tsagaraki, and E. Aperathitis",
EUROMAT 2017, 17-22 September 2017, Thessaloniki, Greece.
- [40]. **Pressure and temperature determination with micromachined GAN/Si SAW based resonators operating in the GHz frequency range**
A. Müller, G. Konstantinidis, A. Stefanescu, I. Giangu, A. Stavriniadis, M. Pasteanu, G. Stavriniadis and A. Dinescu,
Proceedings of 19th International Conference in Solid-State Sensors, Actuators and Microsystems (TRANSDUCERS 2017)
- [41]. **High sensitivity, GHz operating SAW pressure sensor structures manufactured by micromachining and nano-processing of GaN/Si**
A.Müller, A. Stavriniadis, I. Giangu, A. Stefanescu, G. Stavriniadis, A. Pantazis, A. Dinescu, G. Boldeiu, G. Konstantinidis
Intl Microwave Symposium IMS 2016, San Francisco, May 2016
- [42]. **GHz operating GaN based SAW resonators for pressure and temperature sensing**
A. Müller, G. Konstantinidis, I. Giangu, A. Stefanescu, G. Stavriniadis, A. Dinescu, S. Iordanescu, A. Stavriniadis
SAW symposium 2016, Oct 20-21, Dresden, Germany
- [43]. **Capacitances in 4H SiC TSI-VJFETS**
M. Kayambaki, K. Vamvoukakis, A. Stavriniadis, G. Konstantinidis, N. Kornilios, K. Zekentes
10th ECSCRM, Chalkidiki, Greece, September, 2016

- [44]. **Salicide-like process for the formation of gate and source contacts in 4H-SiC TSI-VJFETs**
A Stavriniadis, G. Konstantinidis, K. VAmvoukakis, K. Zekentes
10th ECSCRM, Chalkidiki, Greece, September, 2016
- [45]. **Electrical characterization of individual gallium nitride nanopillars synthesized by plasma assisted molecular beam epitaxy**
G. Doundoulakis, A. Stavriniadis, S. Eftychis, J. Kruse, M. Androulidaki, K. Tsagaraki, M. Kayambaki, G. Konstantinidis, P. Normand, K. Zekentes and A. Georgakilas
11th International Conference on Nitride Semiconductors (ICNS-11), August 30th - September 4th, 2015, Beijing, China
- [46]. **Analysis of device characteristics of thin AlN/GaN/AlN HEMTs grown on sapphire substrates**
Ch. Zervos, A. Adikimenakis, A. Bairamis, A. Kostopoulos, M. Kayambaki, K. Tsagaraki, G. Konstantinidis, and A. Georgakilas
11th International Conference on Nitride Semiconductors (ICNS-11), August 30 - September 4, 2015, Beijing, China
- [47]. **Physics and growth of AlN/GaN HEMT structures on sapphire and diamond substrates**
A. Georgakilas, A. Adikimenakis, Ch. Zervos, A. Bairamis, K. E. Aretouli, K. Tsagaraki, A. Kostopoulos, A. Stavriniadis, E. Tsikritsaki, E. Iliopoulos, and G. Konstantinidis
European Materials Research Society 2015 fall meeting (EMRS 2015), September 15 - 18 Warsaw, Poland
- [48]. **Growth and evaluation of thin AlN/GaN/AlN HEMT structures by molecular beam epitaxy**
A. Bairamis, Ch. Zervos, A. Adikimenakis, A. Kostopoulos, M. Kayampaki, K. Tsagaraki, G. Konstantinidis and A. Georgakilas
11th International Conference on Nitride Semiconductors (ICNS-11), August 30 - September 4, 2015, Beijing, China
- [49]. **Nitrogen containing zinc oxide transparent bipolar devices fabricated on patterned substrates by rf-sputtering**
A. Kostopoulos, G. Konstantinidis, G. Michail, V. Kampylafka, M. Kayambaki, M. Androulidaki, K. Tsagaraki, M. Modreanu, G. Kiriakidis and E. Aperathitis
Symposium N: Synthesis, processing and characterization of nanoscale multifunctional oxide films, E-MRS Spring Meeting, 10-15 May 2015, Lille, France
- [50]. **Near room temperature emission from single (211) B InAs QD and clear anti-bunching behaviour up to 60K**
S. Germanis, L. Monniello, R. Hostein, A. Stavriniadis, G. Konstantinidis, Z. Hatzopoulos, V. Voliotis, N. T. Pelekanos
Book of Abstracts of 30th Panhellenic Conference on Solid-State Physics and Materials Science, Heraklion, Crete, Greece September 2014.
- [51]. **Towards stable zinc oxide and zinc nitride transparent bipolar devices from a single rf-magnetron sputtering zinc nitride target**
E. Aperathitis, G. Doundoulakis, V. Kampylafka, A. Kostopoulos, G. Konstantinidis, M. Kayambaki, K. Tsagaraki, M. Modreanu, E. Iliopoulos, G. Kiriakidis
WOCS/DICE/EXMATEC 2014, European Cultural Centre, Delphi, Greece, 15-20th June 2014
- [52]. **Zinc oxide transparent bipolar devices fabricated on patterned substrates from a single RF-magnetron sputtering zinc nitride target**
A. Kostopoulos, G. Konstantinidis, V. Kampylafka, M. Kayambaki, G. Michail, K. Tsagaraki, M. Modreanu, G. Kiriakidis and E. Aperathitis
5th International Symposium on Transparent Conducive Materials (IS-TCM 2014) 12 - 17 October, 2014 Plataniis - Chania, Crete, Greece
- [53]. **Momentum Space Interferences as an Evidence of Remote Quantum Coherence of Condensates**

C. Anton, G. Tosi, M.D. Martin, Z. Hatzopoulos, G. Konstantinidis, P. Eldridge, P. Savvidis, C. Tejedor, L. Vina, ICPS 2014

Austin Texas, USA, Aug 2014

[54]. Stark effect on the emission of a single piezoelectric InAs quantum dot at liquid nitrogen temperature

S. Germanis, C. Katsidis, A. Stavriniadis, S. I. Tsintzos, G. Konstantinidis, Z. Hatzopoulos, N. T. Pelekanos
Book of Abstracts of the International Conference on Physics of Semiconductors 2014, ICPS 14, Austin, August 2014

[55]. Near RT emission from a single piezoelectric InAs quantum dot and temperature dependent anti-bunching experiments

S. Germanis, L. Monniello, R. Hostein, A. Stavriniadis, G. Konstantinidis, Z. Hatzopoulos, V. Voliotis, N. T. Pelekanos
Book of Abstracts of the International Conference on Physics of Semiconductors 2014, ICPS 14, Austin, Texas, USA, August 2014

[56]. AlN/GaN/AlN double heterostructures with thin AlN top barriers

Ch. Zervos, A. Bairamis, A. Adikimenakis, A. Kostopoulos, M. Kayampaki, K. Tsagaraki, G. Konstantinidis and A. Georgakilas
10th International Conference on Advanced Semiconductor Devices and Microsystems" (ASDAM 2014), Smolenice Castle, Slovakia, October 20-22, 2014

[57]. Realization of AlN/GaN HEMTs on selectively grown Ga-polarity GaN thin films on polycrystalline diamond substrates by PAMBE

A. Georgakilas, K. E. Aretouli, K. Tsagaraki, A. Kostopoulos, A. Stavriniadis, G. Konstantinidis and Adam Adikimenakis
18th International Conference on Molecular Beam Epitaxy" (MBE 2014), Flagstaff, Arizona, September 7-12, 2014

[58]. Effects of Al cap layers and HCl treatment on contacts on AlN/GaN 2DEG heterostructures

Ch. Zervos, A. Adikimenakis, F. Miziou, A. Bairamis, M. Kayambaki, A. Kostopoulos, G. Konstantinidis, and A. Georgakilas
International Workshop on Nitride Semiconductors" (IWN 2014), Wroclaw, Poland, August 24-29, 2014

[59]. AlN/GaN HEMTs with thin GaN/AlN buffer layers on sapphire (0001) substrates

Ch. Zervos, A. Bairamis, A. Adikimenakis A. Kostopoulos, M. Kayampaki, K. Tsagaraki, G. Konstantinidis and A. Georgakilas,
38th Workshop on Compound Semiconductor Devices and Integrated Circuits (WOCSDICE 2014), Delphi, Greece, June 15-18, 2014

[60]. PAMBE of Ga-polarity (0001) GaN films on polycrystalline diamond substrates and realization of AlN/GaN HEMTs

A. Georgakilas, K. E. Aretouli, K. Tsagaraki, A. Kostopoulos, A. Stavriniadis, G. Konstantinidis and A. Adikimenakis,
International Workshop on Nitride Semiconductors" (IWN 2014), Wroclaw, Poland, August 24-29, 2014

[61]. Ultra-shallow and high-density two-dimensional electron gas channels for HEMTs based on the AlN/GaN heterojunction

A. Adikimenakis, K.E. Aretouli, K. Tsagaraki, A. Kostopoulos, A. Stavriniadis, G. Konstantinidis, E. Iliopoulos and A. Georgakilas
4th International Conference from Nanoparticles and Nanomaterials to Nanodevices and Nanosystems" (IC4N), Corfu, Greece, June 16-20, 2013

[62]. Epitaxial Ga-polarity AlN/GaN (0001) HEMTs on polycrystalline diamond substrates

A. Georgakilas, K. E. Aretouli, K. Tsagaraki, A. Adikimenakis, A. Kostopoulos, A. Stavriniadis and G. Konstantinidis
38th Workshop on Compound Semiconductor Devices and Integrated Circuits" (WOCSDICE 2014), Delphi, Greece, June 15-18, 2014

- [63]. Spontaneous growth of III-V semiconductor nanopillars by molecular beam epitaxy for nanoelectronic, photonic and sensor applications**
A. Georgakilas, A. Adikimenakis, S. Eftychis, J. E. Kruse, K. Tsagkaraki, M. Androulidaki, E. Iliopoulos, Z. Hatzopoulos, P. Tzanetakis, Ph. Komninou, T. Koukoulas, Th. Kehagias, G. P. Dimitrakopoulos, J. Kioseoglou, A. Lotsari, Th. Karakosas, G. Konstantinidis, G. Doundoulakis, K. Zekentes, P. Dimitrakis, V. Ioannou Sougleridis, A. Olziersky, P. Normand
4th International Conference from Nanoparticles and Nanomaterials to Nanodevices and Nanosystems (IC4N), 2013, Corfu, Greece
- [64]. Ballistic graphene nanostructures for radio wave detection**
G. Deligeorgis, F. Coccetti and G. Konstantinidis
4th International conference from Nanoparticles and Nanomaterials to Nanodevices and Nanosystems (IC4N), 16 – 20 June 2013, Corfu Greece
- [65]. High electron mobility transistors based on heteroepitaxy of GaN (0001) on diamond substrates**
A. Adikimenakis, K. E. Aretouli, K. Tsagaraki, A. Kostopoulos, A. Stavriniadis, G. Konstantinidis and A. Georgakilas,
Fifth International Conference on Micro-Nanoelectronics, Nanotechnologies and MEMS" (Micro&Nano 2012), Heraklion, Greece, October 7-10, 2012
- [66]. Piezoelectric (211) B InAs quantum dots for single photon emitters at room temperature**
S. Germanis, A. Beveratos, A. Stavriniadis, G. Konstantinidis, Z. Hatzopoulos, N.T. Pelekanos
Proceedings of Optics of Excitons in Confined Systems 2013, Rome, September 2013
- [67]. Piezoelectric InAs/GaAs quantum dots for high temperature single photon emission**
S. Germanis, A. Beveratos, A. Stavriniadis, G. Konstantinidis, Z. Hatzopoulos, N. T. Pelekanos
Book of Abstracts of PLMCN 2013, Hersonissos, Crete, Greece
- [68]. The role of polarization fields in hysteresis phenomena in double barrier Al(Ga)N/GaN resonant tunneling diodes**
Ch. Dimizas, P. Dimitrakis, G. Deligeorgis, G. Konstantinidis and E. Iliopoulos
WOCS DICE 2013, Warnemünde, Germany, May 2013
- [69]. A novel (211) B InAs quantum dot system with negligible fine structure splitting for the generation of entangled photon pairs**
S. Germanis, A. Beveratos, G. E. Dialynas, A. Stavriniadis, Z. Hatzopoulos, G. Konstantinidis, N.T. Pelekanos
Book of Abstracts of the 5th International Conference on Micro-Nanoelectronics, Nanotechnologies and MEMS, Kokkini Hani, Crete, Greece, October 2012
- [70]. Graphene nanoribbon ballistic devices for RF detection**
G. Deligeorgis, F. Coccetti, G. Konstantinidis and R. Plana
European Conference/Workshop on the Synthesis, Characterization and Applications of Graphene 27-30 September 2012, Mykonos, Greece
- [71]. Comparative study of AlN dielectric films' electrical properties for MEMS capacitive switches**
M. Koutsourelis, A. Adikimenakis, L. Michalakis, E. Papandreou, G. Stavriniadis, G. Konstantinidis, A. Georgakilas and G. Papaioannou
MICRO & NANO 2012, Heraklion, October 7-10, 2012
- [72]. High electron mobility transistors based on heteroepitaxy of GaN (0001) on diamond substrates**
A. Adikimenakis, K. E. Aretouli, K. Tsagaraki, A. Kostopoulos, A. Stavriniadis, G. Konstantinidis and A. Georgakilas
5th International Conference on Micro-Nanoelectronics, Nanotechnologies & MEMS", (MICRO & NANO 2012), Heraklion, October 7-10, 2012
- [73]. Surface properties and electrical behavior of Cr contacts on MOCVD and MBE grown p-type GaN**

F. G. Kalaitzakis, G. Konstantinidis, L. Sygellou, S. Kennou, S. Ladas, N. T. Pelekanos
Proceedings of HETECH 2010, Fodele, Crete, Greece, October 2010

[74]. Transparent TFT & p/n diode from a single ZnN target

E. Aperathitis, V. Kambilafka, A. Kostopoulos, M. Androulidaki, K. Tsagaraki, M. Modreanu and G. Konstantinidis

4th International Conference on Micro-Nanoelectronics, Nanotechnologies & MEMs, NCSR Demokritos, Athens, 12 – 15 December 2010

[75]. Negative differential resistance and charge trapping phenomena in (0001) Al(Ga)N/GaN double barrier resonant tunneling diodes

G. Deligeorgis, P. Dimitrakis, X. Dimizas, A. Kostopoulos, G. Konstantinidis, R. Normand and E. Iliopoulos
MICRO & NANO 2010, Athens, Greece, December 2010

[76]. Pulsed I-V performance of AlN/GaN HEMTs

K.E. Aretouli, J. Kuzmik, D. Pogany, A. Adikimenakis, T. Kostopoulos, G. Konstantinidis, A. Georgakilas
MICRO & NANO 2010, Athens, December 12-15, 2010

[77]. Epitaxial growth of (0001) GaN heterostructures on polycrystalline diamond substrates

A. Adikimenakis, K. Tsagaraki, Th. Kostopoulos, G. Konstantinidis, K.E. Aretouli, G. Tsiakatouras, E. Dynowska, E. Kaminska and A. Georgakilas

4th International Conference on Micro-Nanoelectronics, Nanotechnologies & MEMs" (MICRO & NANO 2010), Athens, December 12-15, 2010

[78]. Electromagnetic Propagation in Graphene in the mm-wave Frequency

Range D. Neculoiu, G. Deligeorgis, M. Dragoman, D. Dragoman, G. Konstantinidis, A. Cismaru and R. Plana
2010 European microwave integrated circuits conference (EUMIC) European Microwave Integrated Circuits Conference Proceedings pp.377-380 (2010)

[79]. Epitaxial growth of (0001) GaN films on polycrystalline diamond substrates by plasma assisted MBE

A. Adikimenakis, K. Tsagaraki, Th. Kostopoulos, G. Konstantinidis, K.E. Aretouli, G. Tsiakatouras, E. Dynowska, E. Kaminska and A. Georgakilas

HETECH 2010, October 18-20, 2010, Fodele, Crete, Greece

[80]. Current instabilities in AlN/GaN HEMTs

K.E. Aretouli, J. Kuzmik, D. Pogany, A. Adikimenakis, T. Kostopoulos, G. Konstantinidis and A. Georgakilas

HETECH 2010, October 18-20, 2010, Fodele, Crete, Greece

[81]. Micromachined III-N acoustic devices for bacteria detection

A.K. Pantazis, E. Gizeli, D. Vasilache, E. Aperathitis, A. Müller and G. Konstantinidis

10th International Symposium on RF MEMs and RF Microsystems, MEMSWAVE 2009, Trento 6-9 July, 2009, Italy

[82]. Study of capabilities and limitations of the AlN/GaN HEMT material system

A. Adikimenakis, K. Aretouli, A. Kostopoulos, E. Iliopoulos, K. Tsagaraki, A. Ajaguna, G. Konstantinidis and A. Georgakilas

IWN 2008, Montreux, Switzerland, October 6-10, 2008

[83]. High electron mobility transistors based on the AlN/GaN heterojunction

A. Adikimenakis, K. Aretouli, M. Alomari, E. Kohn, A. Kostopoulos, E. Iliopoulos, K. Tsagaraki, A. Ajaguna, G. Konstantinidis and A. GEORGAKILAS

34th International Conference on Micro and nano Engineering 2008" (MNE 2008), Athens, Greece, September 15 -18, 2008

[84]. Negative bi-exciton binding energy in (211)B InAs/GaAs piezoelectric quantum dots

G.E. Dialynas, C. Xenogianni, E. Trichas, P.G. Savvidis, G. Konstantinidis, Z. Hatzopoulos, N.T. Pelekanos

Conference on Lasers and Electro-Optics/Quantum Electronics and Laser Science Conference 2007 Technical Digest, #JTuA6, Baltimore (2007)

- [85]. Growth and characterization of $\text{In}_x\text{Al}_{1-x}\text{N}/\text{GaN}$ heterostructures, throughout the whole composition range, by plasma-assisted MBE**
A. Adikimenakis, E. Iliopoulos, C. Giesen, G. Tsiakatouras, K. Tsagaraki, G. Konstantinidis and A. Georgakilas
3rd Int. Conf. on Micro- Nanoelectronics, Nanotechnology and MEMs" (Micro&Nano 2007), Athens, November 18-21, 2007
- [86]. Properties of Si-doped GaN and AlGaN/GaN heterostructures grown by RF-MBE on high resistivity Fe-doped GaN**
A. Adikimenakis, E. Iliopoulos, M. Zervos, T. McMullen, G. Konstantinidis and A. Georgakilas
Int. Workshop on Nitride Based Nanostructures", February 6-8, 2007, Berlin, Germany
- [87]. Gate-lag and drain-lag effects in InAlN/GaN and GaN/InAlN/GaN HEMTs**
J. Kuzmik, J.-F. Carlin, M. Gonschorek, A. Kostopoulos, G. Konstantinidis, G. Pozzovivo, S. Golka, A. Georgakilas, N. Grandjean, G. Strasser, and D. Pogany
IWN 2006, October 22-27, 2006 Kyoto, Japan
- [88]. Ion Selective Sensors Based on AlGaN/GaN HEMTs**
Y. Alifragis, A. Volosirakis, N.A. Chaniotakis, G. Konstantinidis, E. Iliopoulos and A. Georgakilas
4th International Workshop on Nitride Semiconductors 2006 (IWN2006), October 2006, Kyoto, Japan
- [89]. Properties of Si-doped GaN and AlGaN/GaN heterostructures grown by RF-MBE on high resistivity Fe-doped GaN**
A. Adikimenakis, E. Iliopoulos, M. Zervos, T. McMullen, G. Konstantinidis and A. Georgakilas
EW3NS, September 18-20, 2006, Heraklion, Greece
- [90]. Effects of scaling the physical parameters of AlGaN/GaN high electron mobility pH sensors on their performance**
G. Konstantinidis, Y. Alifragis, E. Iliopoulos, M. Zervos, A. Adikimenakis, N.A. Chaniotakis and A. Georgakilas
EW3NS, September 18-20, 2006, Heraklion, Greece
- [91]. Ion Selective Sensors Based on AlGaN/GaN HEMTs**
Y. Alifragis, A. Volosirakis, A. Georgakilas, G. Konstantinidis, E. Iliopoulos and N.A. Chaniotakis
European Workshop on III-Nitride Semiconductor Materials and Devices (EW3NS), September 18-20, 2006, Heraklion, Greece
- [92]. Potassium selective chemically modified field effect transistors based on AlGaN/GaN two-dimensional electron gas heterostructures**
Y. Alifragis, A. Volosirakis, N. A. Chaniotakis, G. Konstantinidis, A. Adikimenakis and A. Georgakilas
EMRS 2006 Spring Meeting, Symposium Q, Nice, France, May 29 – June 2, 2006
- [93]. Ohmic contacts to p-type GaN**
F. Kalaitzakis, G. Konstantinidis, N. Pelekanos
Proc. European Workshop on III-Nitride Semiconductor materials and devices, Hersonissos Crete, Greece (2006)
- [94]. Development of anion selective ChemFETS based on AlGaN/GaN high electron mobility transistors**
Y. Alifragis, A. Georgakilas, G. Konstantinidis, E. Iliopoulos, A. Kostopoulos, and N. A. Chaniotakis,
PITTCOON 2006, March 2006, Orlando, Florida, USA
- [95]. Effects of scaling the physical parameters of AlGaN/GaN high electron mobility pH sensors on their performance**
Y. Alifragis, A. Georgakilas, G. Konstantinidis, E. Iliopoulos, M. Zervos and N.A. Chaniotakis,
EMRS 2006 Spring Meeting, Symposium Q: Chemical & Biochemical Sensing Transistors: from Materials to Systems, Nice, France, May 29 – June 2, 2006
- [96]. High sensitivity AlGaN/GaN high electron mobility transistor-based sensors for pH measurements**
Y. Alifragis, A. Georgakilas, G. Konstantinidis, E. Iliopoulos, A. Kostopoulos and N.A. Chaniotakis

4th Instrumental Methods of Analysis, Modern Trends and Applications (IMA 2005), Chersonissos, Heraklion, Greece, October 2-6, 2005

[97]. Properties of GaN and AlGaN/GaN Heterostructures Grown by Plasma-assisted Molecular Beam Epitaxy

E. Iliopoulos, A. Adikimenakis, E. Dimakis, T. McMullen, K. Tsagaraki, M. Androulidaki, M. Zervos, G. Konstantinidis and A. Georgakilas

14th International Workshop on Heterostructure Technology (HETECH 05), Smolenice, Slovakia, October 2-5, 2005

[98]. Design and fabrication of AlGaN/GaN high electron mobility transistor sensors for analysis of aqueous nano- and pico-droplets

Y. Alifragis, E. Iliopoulos, M. Zervos, A. Adikimenakis, M. Sfendourakis, N. Chaniotakis, G. Konstantinidis and A. Georgakilas

14th International Workshop on Heterostructure Technology (HETECH 05), Smolenice, Slovakia, October 2-5, 2005

[99]. Technology, Properties and Limitations of State-of-the-art InAlN/GaN HEMTs

J. Kuzmík, J. -F. Carlin, T. Kostopoulos, G. Konstantinidis, A. Georgakilas, D. Pogany

63rd Device Research Conference (DRC '05), Santa Barbara, June 20-22, 2005

[2.4]. OTHER INVITED LECTURES

[1]. Nanoelectronics at FORTH

G. Konstantinidis

Invited by the Stewart Blusson Quantum Matter Institute - University of British Columbia, March 2018

[2]. Funding opportunities for dual technologies

G. Konstantinidis

Invited by the National Defense Systems of Greece, March 2016

[3]. MRG activities

G. Konstantinidis

Invited at the Advanced Technology Center of the University of Surrey, October 2013

[4]. Acoustic devices based on micromachining and nanoprocessing of GaN/Si

A. Müller, G. Konstantinidis,

Romanian National Seminar on Nanoscience and Nanotechnologies, Bucharest, May 2013

[5]. Wide band gap microsystems

G. Konstantinidis

Invited by METUniversity, Ankara, May 2010

[6]. Micromachining and nanoprocessing of GaN/Si for GHz acoustic resonators and UV photodetecting applications

A. Müller, G. Konstantinidis, D. Neculoiu

Romanian National Seminar on nanoscience and nanotechnology, Romanian Academy, February 2010

[7]. Market potential of the research results of MRG

G. Konstantinidis

Invited by the "Invest in Greece" government activity, Heraklion, Crete, November 2008

[8]. III-Nitrides related activities at MRG

G. Konstantinidis

Invited to the Ferdinand Braun Institute, Berlin, November 2008

[9]. GHz SAW and FBAR devices manufactured using micromachining and nanoprocessing of wide band gap semiconductors

A. Müller, G. Konstantinidis

National seminar of nanoscience and nanotechnology. Romanian Academy, Bucharest, March 2008

[10]. Current trends in nanoelectronics

G. Konstantinidis

Workshop on radiation and humans, Technical Educational Institute of Crete, Heraklion, February 2008

[11]. MEMS activities at MRG

G. Konstantinidis

Theon Sensors SA, Athens, July 2005

[12]. III-V semiconductors: Light & communications

G. Konstantinidis

Open day for New Technologies, Technical Educational Institute of Athens, Athens, April 2004

[13]. MRG activities for high frequency applications

G. Konstantinidis

Invited by the School of Physics & Astronomy, Cardiff University, Cardiff, Mar 2003

[14]. ISO 9001 and compound semiconductor MMIC fabrication

G. Konstantinidis

Invited by INTRACOM SA, Korwpi, Athens, Mar 2002

[15]. MRG research results with dual potential

G. Konstantinidis

FORTH-French Embassy meeting, Heraklion, December 2001
